

Nokia Customer Care

7 - System Module

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Glossary of Terms

ACI	Accessory Control Interface
ADC	Analogue to Digital Converter
AFC	Automatic Frequency Control
ASIC	Application Specific Integrated Circuit
ASM	Antenna switch module
BB	Baseband
BSI	Battery Size Indicator
DCT4	Digital Core Technology, generation 4
DSP	Digital Signal Processor
DUT	Device under test
EDGE	Enhanced Data Rates for Global Evolution
EGPRS	Enhanced General Packed Radio Service
EMC	Electro Magnetic Compatibility
ESD	Electro Static Discharge
FC	Functional Cover
FR	Full Rate
GMSK	Gaussian Minimum Shift Keying
GPRS	General Packed Radio Service
GSM	Global System for Mobile Communication
GSM900	GSM900 (channels 1 - 124)+extended GSM900 (channels 975 - 1023, 0)
HSCSD	High Speed Circuit Switched Data
HW	Hardware
IF	Interface
IHF	Integrated Hands Free

IMEI	International Mobile Equipment Identity
I/O	Input/Output
IR	Infrared
IrDA	Infrared Data Association
LCD	Liquid Crystal Display
LED	Light Emitting Diode
LDO	Low Drop Out
LNA	Low Noise Amplifier
LO	Local Oscillator
MCU	Micro Controller Unit
PA	Power Amplifier
Phoenix	SW tool of DCT4
PLL	Phase Locked Loop
PWB	Printed Wired Board
RF	Radio Frequency
RTC	Real Time Clock
RX	Receiver
SA	Spectrum analyzer
SIM	Subscriber Identification Module
SW	Software
TP	Test point
TX	Transmitter
UEMEK	Universal Energy Management ASIC enhanced version
UI	User Interface
UPP	Universal Phone Processor
USB	Universal Serial Bus

VBU _{<COFF>}	Back-up Battery Cut Off voltage (typical: 2.0 V)
VCO	Voltage controlled oscillator
VCTCXO	Voltage controlled temperature compensated oscillator
V _{<MSTR+>}	Master Reset Threshold (typical: 2.1 V)
8-PSK	Phase Shift Keying with 8 states (Modulation scheme for EDGE/ GPRS)

Baseband

The RM-30 product is a DCT4.5 Expression segment phone. There are two variants: An EGSM900/GSM1800/GSM1900 phone and a US variant, RM-31, with GSM850/1800/1900.

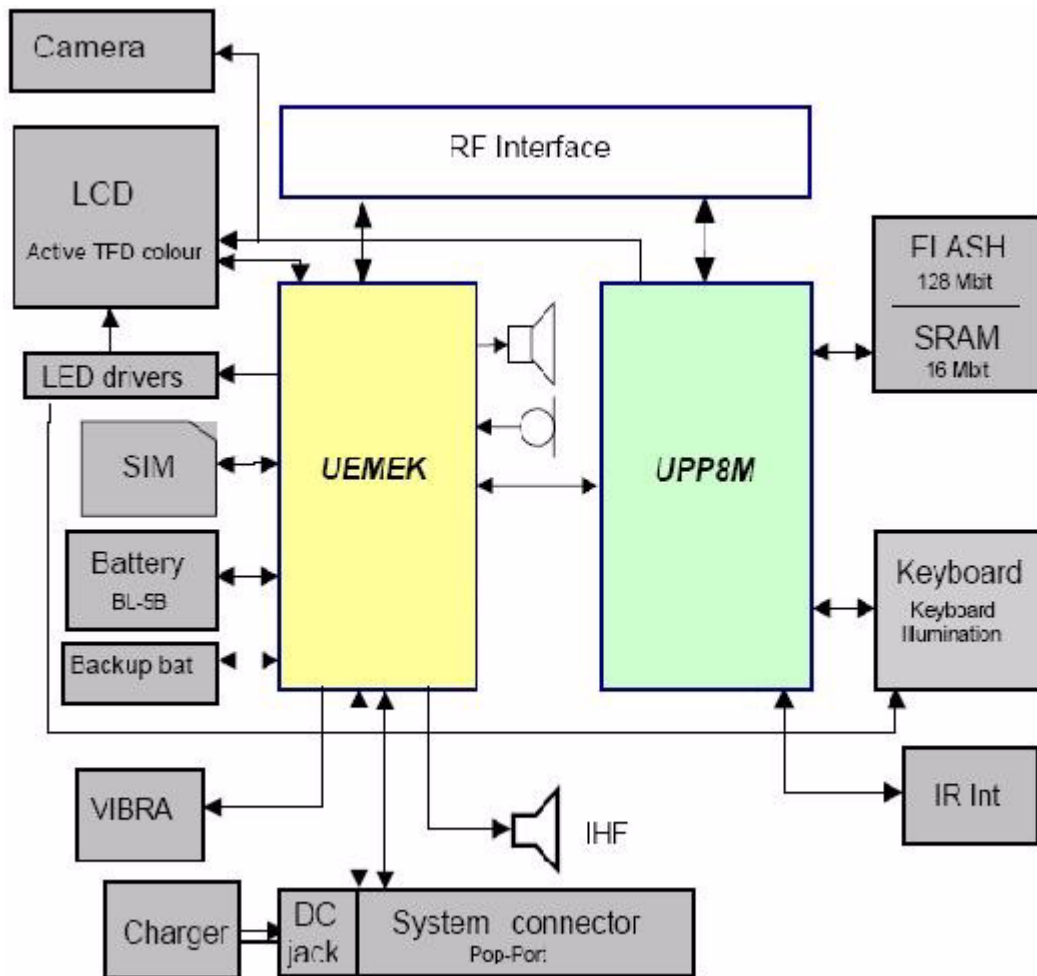
The HW has the following features:

- GPRS and HSCSD with EDGE in up to (2RX + 2TX) (MCS5), without EDGE also in (3RX + 1TX) (MCS6)
- DCT4 with AMR and 16 MIDI tones
- 128/16 Mbit Combo memory
- Amazon Active display with 64k colours
- Battery BL-5B
- Illuminated XPress on grips
- PopPort™ interface
- 5-way navigation key with select
- FCI rear side (C-cover)
- VGA Camera
- Vibra
- IHF

The RM-30 BB is based on the DCT4/4.5 engine and is compatible to the PopPort™ accessories. The DCT4/4.5 engine consists basically of two ASICs. The UEMEK (Universal Energy Management IC including voltage regulators, charge control and audio circuits, audio IFH amplifier from DCT4.5) and the UPP (Universal Phone Processor including MCU, DSP and RAM from DCT4).

■ **Block diagram**

Figure 1:Baseband block diagram



UEMEK supplies both baseband and RF with power via built in voltage regulators, which are connected to the battery. The RF parts use mainly 2.78 V and the baseband parts 1.8V I/O voltage. The UPP core is supplied with programmable core voltage of 1.0V, 1.3V or 1.5V. UEMEK includes 7 linear LDO (Low Drop-Out) regulators for baseband and 7 regulators for RF. It also includes 4 current sources for biasing purposes and internal usage. The UEMEK is furthermore supplying the SIM interface with a programmable voltage of 1.8V or 3V.

Note: 5V SIM cards are no longer supported by DCT-4 generation Baseband.

UPP operates from a 26 MHz clock coming from the RF ASIC Helgo. The clock signal is divided by two down to the nominal system clock frequency of 13 MHz. The DSP and MCU contain PLLs, which can multiply the system clock to a higher frequency.

A real time clock function is integrated into the UEMEK, which utilizes the same 32kHz clock supply as the sleep clock.

The communication between UEMEK and UPP is implemented using two bi-directional serial busses, CBUS and DBUS. The CBUS is controlled by the MCU and operates at a speed of 1 MHz. The DBUS is controlled by the MCU and operates at a speed of 13 MHz. Both processors are located in the UPP.

The UEMEK ASIC handles the analog interface between the Baseband and the RF section. UEMEK provides A/D and D/A conversion of the in-phase and quadrature receive and transmit signal paths and also A/D and D/A conversions of received and transmitted audio signals to and from the user interface. The UEMEK supplies the analog TXC and AFC signals to the RF section according to UPP signal control. There are also separate signals for PDM coded audio. Digital speech processing is handled by the DSP inside UPP ASIC.

UEMEK is a dual voltage circuit, the digital parts are running from the baseband supply 1.8V and the analog parts are running from the analog supply 2.78V or backup battery. Also VBAT is directly used (Vibra, LED-driver, Camera Regulator).

The Baseband supports both internal and external microphone inputs and speaker outputs. Keypad tones, DTMF, and other audio tones are generated and encoded by the UPP and transmitted to the UEMEK for decoding. An external vibra alert control signals are generated by the UEMEK with separate PWM outputs.

EMC shielding is implemented using a soldered shielding, RF cans and PWB grounding.

Environmental Specifications

■ Absolute maximum ratings

Table 1: Absolute maximum ratings

Signal	Note
Battery Voltage (Idle)	-0.3...5.5V
Battery Voltage (Call)	Max 4.8V
Charger Input Voltage	-0.3V ...16V

■ Temperature conditions

Table 2: Temperature conditions

Condition	Min	Max
Normal operating temperature	-10°C	+55°C
Reduced functionality	-25°C	+75°C
Storage	-40°C	+85°C

■ Humidity and water resistance

Table 3: Humidity conditions

Condition	Min	Max
Relative Humidity	5%	95%

The module is not protected against water.

■ **Frequencies in baseband**

Table 4: Frequencies in baseband

Frequency	Context	UPP	UEMEK	Flash	SIM	Comment
32 kHz	SleepClk		X			
1 MHz	CBUS	X	X			
Up to 1 MHz	RFConvClk	X	X			Estimation
6,5 MHz	Display IF	X				
3,25 MHz	SIMIF		X		X	Min
13 MHz	DBUS, RFBUClik	X	X			
26 MHz	RF Clk	X				
52 MHz	Memory Clock	X		X		

■ **PWB**

Characteristics of the PWB

- Single PWB
- 8 layer board
- Double side assembled

Key components

Figure 2:Key components

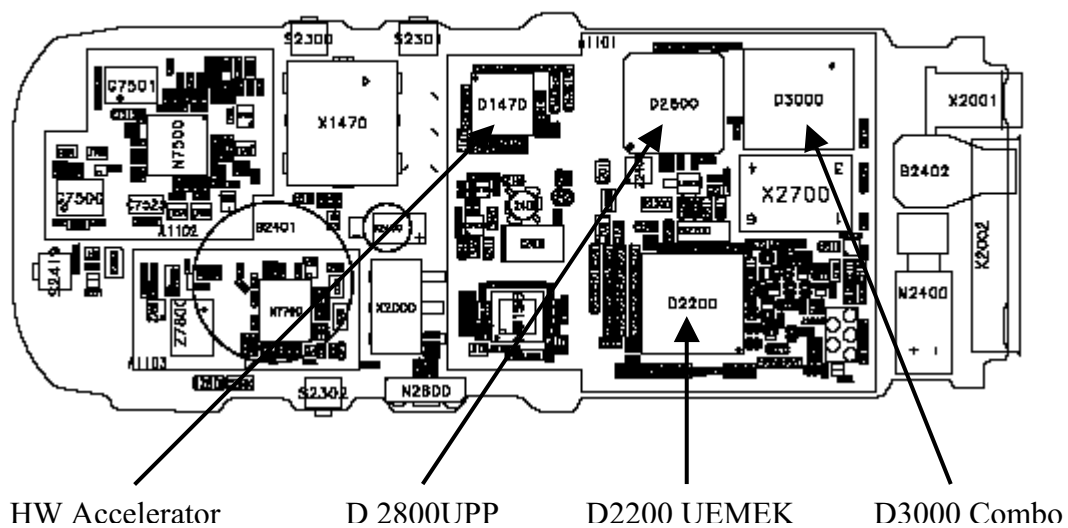


Table 5: Key components

Position	Component Name
D1470	HW Accelerator
D2800	UPP8M V4.2E
D2200	UEMEKv2.0
D3000	Combo Memory (128M NOR + 16M UTRAM)

Technical Specifications

■ Baseband core

UPP

Main characteristics of the used UPP are:

- DSP, LEAD3 16 bit DSP core 32 bit IF max. 200 MHz
- MCU based on ARM7 RISC MCU core max 50 MHz
- Internal 8 Mbit SRAM (PDRAM)
- General purpose UARTS
- SIM card interface
- Accessory interface (ACI)
- Interface control for Keypad, LCD, Audio and UEM control
- Handling of BB-RF Interface

UEMEK

Main characteristics of the used UEMEK are:

- ACI support
- Audio codec
- 11 Channel A/D converter
- Auxiliary A/D converter
- 32 KHz crystal oscillator
- SIM interface and drivers
- Security logic
- Storage of IMEI code
- Buzzer and vibra motor drivers
- PWM
- 2 LED drivers, keyboard and display backlight drivers
- Voltage reference for analogue blocks
- Charging function
- Baseband regulators
- RF regulators
- RF interface converters

External SRAM and Flash

The Combo-Memory is a multi chip package memory which combines 128 Mbit (8Mx16) muxed burst multibank flash and 16 Mbit muxed CMOS PSRAM (Pseudo SRAM: DRAM with SRAM interface).

The combo is supplied by single 1,8 V for read, write and erase operations. For accelerated flash programming, $V_{pp} = 9.0$ V has to be applied to VPP input of the combo device.

The combo memory is housed in a 44-ball FBGA.

■ **Energy management**

The energy management of RM-30 is based on BB 4.0 architecture. A so-called semi fixed battery (BL-5B) supplies power primarily to UEMEK ASIC and the RF PA. The UEMEK includes several regulators to supply RF and Baseband. It provides energy management including power up/down procedure.

Modes of operation

The baseband engine has six different functional modes: Since the UEMEK controls the regulated power distribution; each of these states affects the general functionality of the phone.

1. No supply
2. Backup
3. Acting Dead
4. Active
5. Sleep
6. Charging

No Supply

In *NO_SUPPLY* mode, the phone has no supply voltage. This mode is due to the disconnection of the main battery and backup battery or low battery voltage level in both of the batteries.

The phone is exiting from *NO_SUPPLY* mode when sufficient battery voltage level is detected. The battery voltage can rise either by connecting a new battery with $V_{BAT} > V_{MSTR+}$ or by connecting charger and charging the battery above V_{MSTR+} .

Backup

In *BACKUP* mode the backup battery has sufficient charge but the main battery can be disconnected or empty ($V_{BAT} < V_{MSTR}$ and $V_{BACK} > V_{BU_{COFF}}$).

The VTRC regulator is disabled in *BACKUP* mode. VTRC output is supplied without regulation from the backup battery (VBACK). All the other regulators are disabled.

Acting Dead

If the phone is off when the charger is connected, the phone is powered on but enters a state called "Acting Dead". To the user, the phone acts as if it was switched off. A battery-charging alert is given and/or a battery charging indication on the display is shown to acknowledge the user that the battery is being charged.

Active

In *Active* mode, the phone is in normal operation, scanning for channels, listing to a base station, transmitting and processing information.

Sleep Mode

Sleep mode is entered when both MCU and DSP are in stand-by mode. Both processors control the sleep mode.

The sleep mode is exited either by the expiration of a sleep clock counter in the UEMEK or by some external interrupt, generated by a charger connection, key press, headset connection etc.

In the sleep mode, VCTCXO is shut down and 32 kHz sleep clock oscillator is used as reference clock for the Baseband.

Charging

In RM-30, the battery type/size is indicated by a BSI-resistor. The resistor value corresponds to a specific battery capacity. Also BTEMP, NTC resistor, is located on an engine board.

The battery voltage, temperature, size and current are measured by the UEMEK controlled by the charging software running in the UPP.

The charging control circuitry (CHACON) inside the UEMEK controls the charging current delivered from the charger to the battery. The battery voltage rise is limited by turning the UEMEK switch off when the battery voltage has reached 4.2 V. Charging current is monitored by measuring the voltage drop across a 220 mΩ resistor.

■ Power distribution

Under normal conditions, the battery powers the baseband module. Individual regulators located within the UEMEK regulate the battery voltage VBAT. These regulators supply the different parts of the phone. 7 regulators are dedicated to the RF module and 7 to the baseband module.

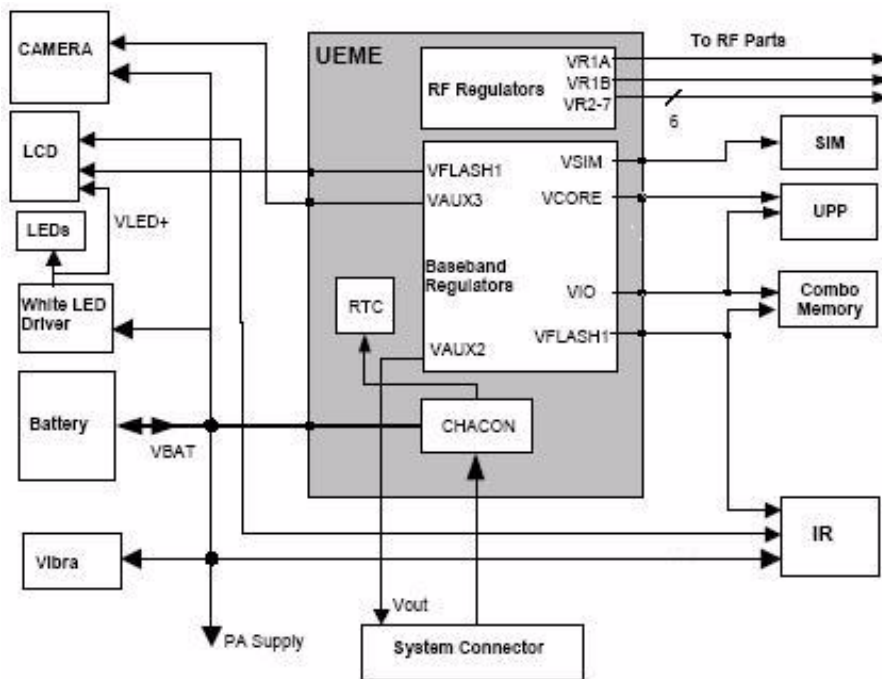
The VSIM regulator is able to deliver both 1,8V and 3,0 V DC and thus supporting two different SIM technologies.

The system connector provides a voltage to supply accessories.

The white LEDs need a higher voltage supply than the battery can supply and are fed by a separate external voltage regulator.

VBAT is directly distributed to the RF power amplifier, FCI and external baseband regulators.

Figure 3: Power Distribution Diagram



■ **DC characteristics**

Supply voltage ranges

Table 6: Battery voltage ranges

Signal	Min	Nom	Max	Note
VBAT	3.1V	3.7V	4.2V	3.2V SW cut off 2.95V HW power off

Baseband regulators

Table 7: Regulator specification

Regulator	Load current (mA)	Limit (V) Min/Max (Typ)
VCORE	200	1.476 / 1.65 (1.57)
VIO	150	1.72 / 1.88 (1.8)
VSIM1	25	1.745 / 1.855 (1.8)
VANA	80	2.70 / 2.86 (2.78)
VFLASH1	70	2.70 / 2.86 (2.78)
VAUX2	70	2.70 / 2.86 (2.78)
VAUX3	10	2.70 / 2.86 (2.78)
VR2	100	2.70 / 2.86 (2.78)
VR3	20	2.70 / 2.86 (2.78)
VR4	50	2.70 / 2.86 (2.78)
VR5	50	2.70 / 2.86 (2.78)
VR6	50	2.70 / 2.86 (2.78)
VR7	45	2.70 / 2.86 (2.78)
VR1A	5*	4.6 / 4.9 (4.75)
VR1B	5*	4.6 / 4.9 (4.75)

* When both enabled. Load current is 10 mA if other is disabled.

Note: This list shows the band regulators only. Please see other descriptions in the Glossary of Terms and in the dedicated sections.

Function Groups

■ Battery

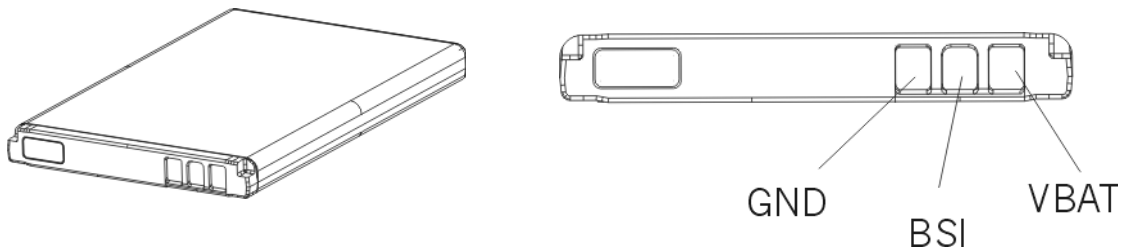
A battery of the type BL-5B is used. It is a Li Ion based standard cell. The battery capacity is 760mAh.

The battery has a three-pin connector. In order to get temperature information of the battery, the NTC mounted on the PWB within the BB area is used.

Ni based batteries are not supported.

The BSI resistor has a nominal value of 75 kOhm.

Figure 4: Battery BL-5B

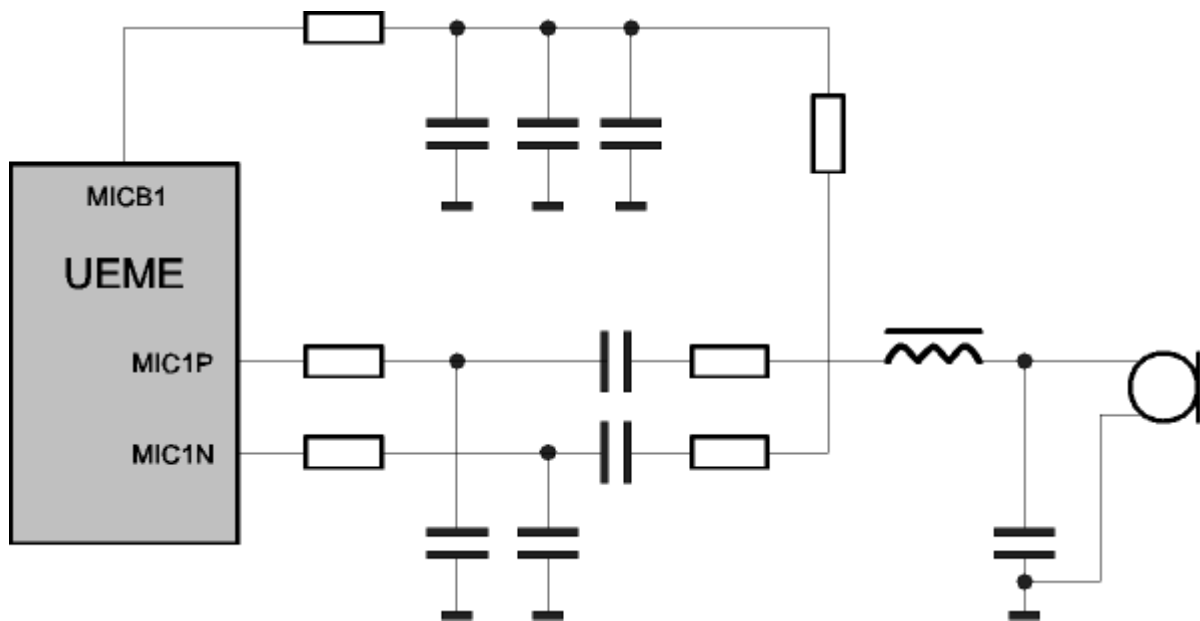


■ Audio

Internal microphone

The internal microphone capsule is mounted to in the PopPort™ system connector. The microphone is omni directional and it's connected to the UEMEK microphone input MIC1P/N. The microphone input is symmetric and the UEMEK (MICB1) provides bias voltage. The microphone input on the UEMEK is ESD protected. Spring contacts are used to connect the microphone to the PWB.

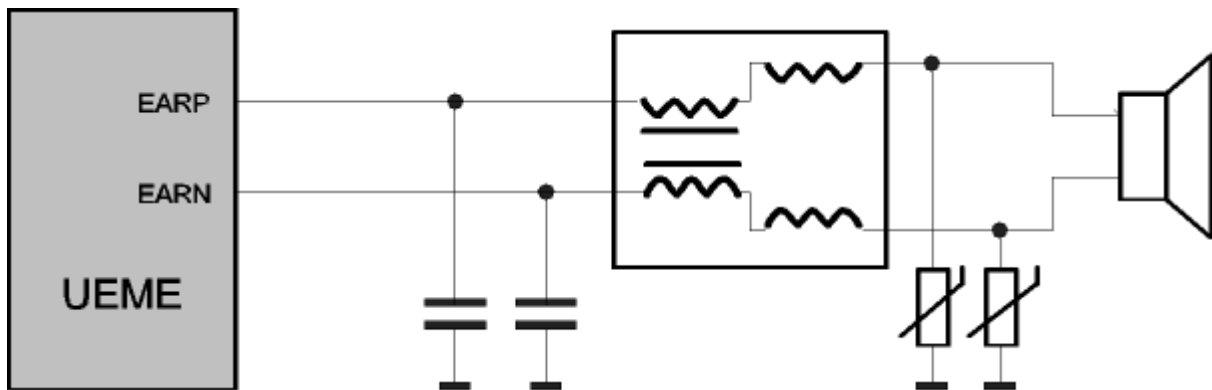
Figure 5: Internal microphone connection



Internal speaker

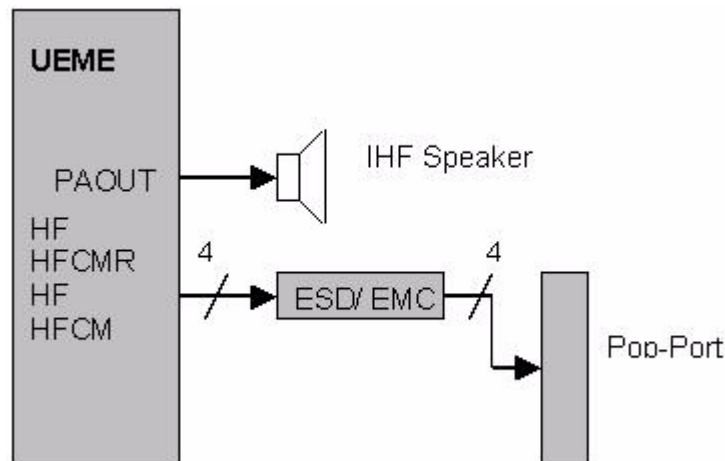
The internal earpiece is a dynamic earpiece with an impedance of 32 ohms. The earpiece is low impedance one since the sound pressure is to be generated using current and not voltage as the supply voltage is restricted to 2.7V. The earpiece is driven directly by the UEMEK and the earpiece driver (EARP & EARN outputs) is a fully differential bridge amplifier with 6 dB gain.

Figure 6: Speaker connection



IHF speaker

UEMEK has an integrated Audio power amplifier to generate output for the IHF speaker. Block diagram of IHF.



For RM-30, the Integrated Hands Free Speaker is used to generate hands free speech, and also polyphonic ringing tones. The speaker capsule is mounted into the A Cover, and spring contacts are used to connect the IHF Speaker contacts to the PWB.

The IHF is furthermore used to generate alerting and warning tones.

External audio

RM-30 is designed to support a fully differential external audio accessory connection. A headset can be directly connected to the PopPort™ system connector. Stereo audio is not supported by RM-30. A stereo headset can be connected to RM-30, since left and right paths are connected in parallel at the PopPort™ connector.

External microphone connection

The external microphone input is fully differential and lines are connected to the UEMEK microphone input MIC2P/N. The UEMEK (MICB2) provides bias voltage. Microphone input lines are ESD protected.

Headset connections

Headset implementation uses separate microphone and earpiece signals. The accessory is detected by the ACI signal when the plug is inserted.

Test possibilities

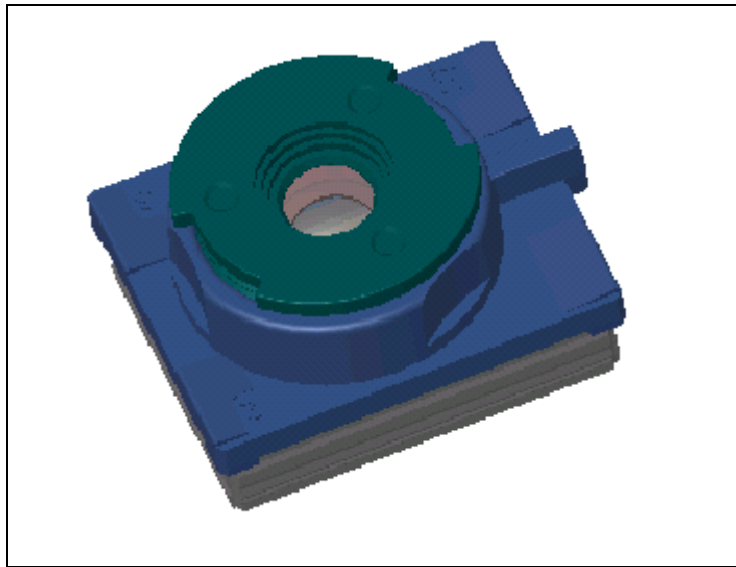
Phoenix audio test

For troubleshooting see Audio faults in Baseband Troubleshooting Instructions.

■ Camera

RM-30 includes a VGA camera module. The camera supports a video preview mode, with integrated colour processing, and high quality still image mode, which utilizes the existing memory and the processing resources of the phone.

Figure 7: Camera module



Key features

- VGA resolution sensor
- On-chip viewfinder
- Video data interface – CCP
- Command interface CCI
- 2,8/1,8 V operation
- On board 11 bit ADC
- Automatic exposure control (AEC)
- Automatic white balance (AWB)
- Small physical size
- Ultra low power standby mode
- On board PLL

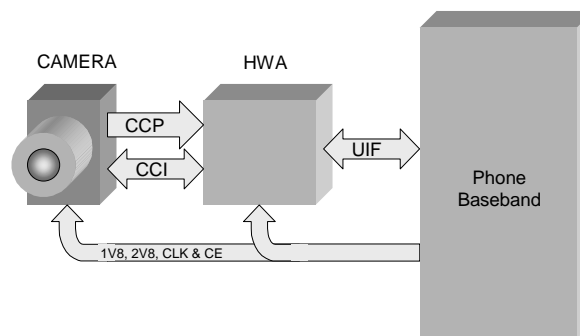
Specifications

Table 8: Camera specification

Feature	Description
Resolution	480 x 640 pixels
Size	10,6 x 8,7 x 5,8 mm
Sensor technology	0,35 μ m HCMOS6i
Pixel size	5,6 x 5,6 μ m
Signal to noise	35 dB @ 100 lux
Minimum illumination	< 10 lux
Lens	f# 2.8 Fixed focus
Power supply	1,7 – 1,9 V Digital 2,7 – 2,9 V Analogue

A separate Hardware Accelerator device is incorporated in the phone system, to run the algorithms in hardware. The HWA performs all tasks to deliver both stills and viewfinder to the Baseband with no further processing required.

Figure 8: Camera module with HW accelerator



CCP bus

CCP, also known as subLVDS, is a differential current mode bus. A CCP connection consists of 2 pairs of differential signals, data and clock, which are routed as 100 Ohm transmission lines and terminated in 100 Ohm at the receiver end.

The CCP is unidirectional and outputs image data only. The data rate is about 117MHz whatever the image size or format.

CCI bus

CCI is an I²C-type bus used as the command interface in CCP/CCI systems. The HWA has a CCI bus master for communicating with the sensor.

UIF bus

UIF is a slow (6,5 MHz) bus which may be shared with other UI functions (e.g. LCD). This version has unidirectional TX and Rx data lines and consists of a chip enable, chip select, Tx data, Rx data, data clock and system clock.

Clocks

The cameras and HWA can use 19.44MHz, 19.2MHz, 16.8MHz and 13MHz clocks in CCP/CCI mode. The cameras can also use the half-frequencies. The HWA can use 16.8MHz, 13MHz, 9.72MHz, 9.6 MHz and 8.4MHz clocks for UIF mode. The clock input for any of the devices can be DC or AC coupled. The camera and HWA is supplied from the same clock input.

Test possibility

Phoenix camera test

For troubleshooting see Camera faults in Baseband Troubleshooting Instructions.

■ **Vibra**

A vibra alerting device is used to generate a vibration signal for an incoming call. The vibra is located in the bottom end of the phone and connection is done with SMD. The vibra is controlled by a PWM signal from the UEMEK. The Frequency can be set to 64, 129, 258 or 520 Hz and duty cycle can vary between 3% and 97%.

Test possibility

Phoenix Vibra Test

■ LCD module

RM-30 has a 130 x 130 16 bpp (bits per pixel) active matrix color display. The number of colours is 64k, i.e. 16 bits. The LCD Interface is using serial 9-bit data transfer. The LCD display is connected to transceiver PWB by board-to-board connector.

Characteristics

Table 9: LCD Characteristics

Active display area format		130 columns x 130 rows
UserInterface display area format		128 columns x 128 rows
Module size (width x height x thickness)		33,9 mm x 41.3 mm x 3.225 mm
Interface		9-bit serial
Illumination mode		Transflective, Normally white
Number of LEDs		3 white LED
Numbers of colors supported by interface	Full mode	65K 16-bit 5xR, 6xG, 5xB
Pixel height to width ratio		1:1
Viewing direction		6 o'clock
Refresh rate		55 Hz +- 10%

LCD connector

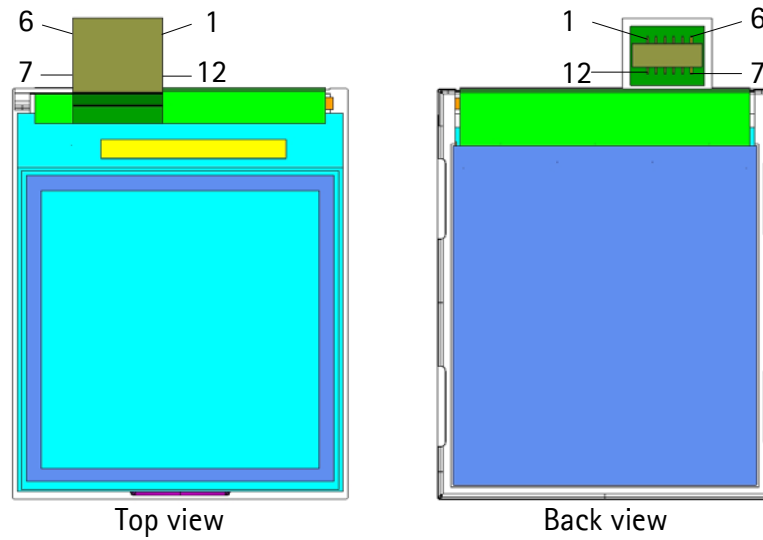
The TE signal is not used.

Table 10: LCD connector

Pin No:	Description	Type	Symbol	Parameter	Min	Typical	Max	Unit
1	Power supply	OUT	VLED-	LED power supply current		15		mA
2	Power supply voltage	IN	VDDI	Operating voltage	1.65	1.8	1.95	V
3	Ground	-	GND					
4	Bidirectional serial data	I/O	SDA	Input voltage high	0.7 x VDDI		VDDI	V
Input voltage low				0		0.3 x VDDI		
Output voltage high @ - 1.0 mA				0.8 x VDDI		VDDI		
Output voltage low @ - 1.0 mA				0		0.2 x VDDI		
5	Chip select	IN	CSX	Input voltage high	0.7 x VDDI		VDDI	V
Input voltage low				0		0.3 x VDDI		
6	Ground	-	GND					
7	TE output to synchronise MCU to frame writing	OUT	TE	Output voltage high @ - 1.0 mA	0.8 x VDDI		VDDI	V
Output voltage low @ - 1.0 mA				0		0.2 x VDDI		
8	Reset	IN	RESX	Input voltage high	0.7 x VDDI		VDDI	V
Input voltage low				0		0.3 x VDDI		
9	Serial clock	IN	SCL	Input voltage high	0.7 x VDDI		VDDI	V
Input voltage low				0		0.3 x VDDI		
10	Ground	-	GND					
11	Power supply voltage	IN	VDD	Operating voltage	2.6	2.75	2.9	V
12	Power supply	IN	VLED+	LED power supply current		15		mA

Figure 9:LCD display

Connector type (Plug) Hirose DF23C-12DP-0.5V



Test possibility

Phoenix Display Test

For troubleshooting see Display faults in Baseband Troubleshooting Instructions.

■ **Keypad**

The RM-30 keys are connected to the UPP via the KEYB(10:0) bus. The keypad consists of a 5x4 matrix of 5 rows, ROW0 – ROW4, and 4 columns, COL1 – COL4.

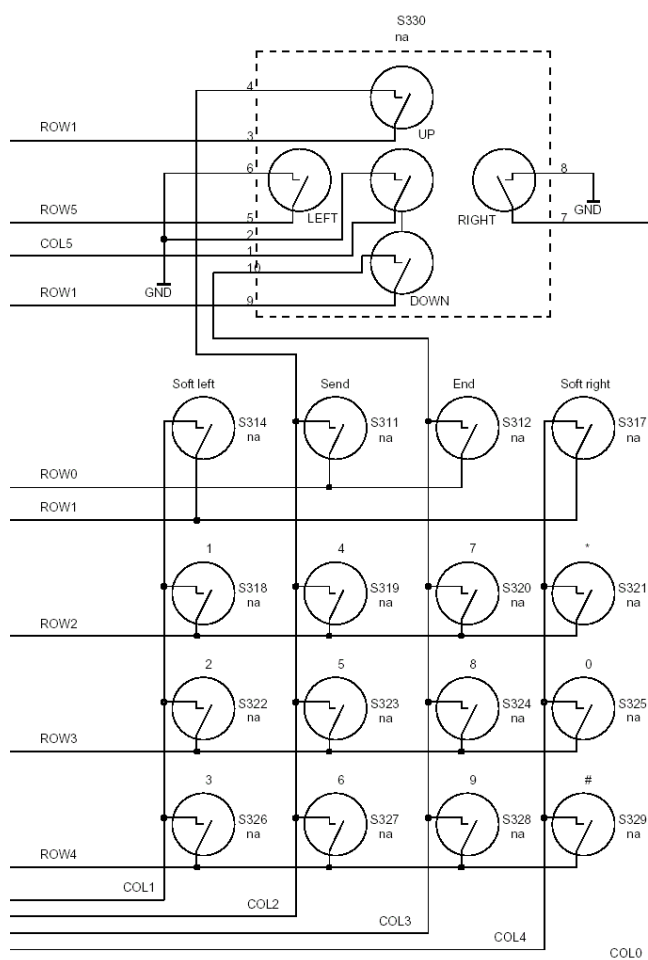
Additionally, there are 3 lines that are directly connected to the UPP IO and can be detected independently. COL5 is connected to GENIO0.

Test possibility

Phoenix Keyboard Test

For troubleshooting, see Keypad faults in Baseband Troubleshooting Instructions.

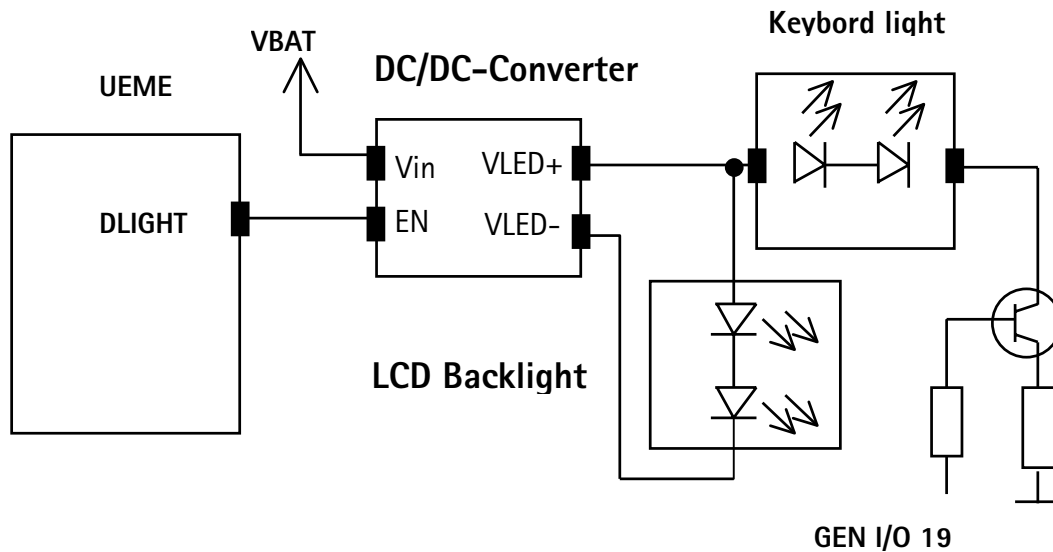
Figure 10:RM-30 keypad



■ **Illumination**

In RM-30, white LED's are used for the LCD backlight and keypad lighting. Three LED's are used for the LCD lighting and two LED's for the keyboard. A step up DC-DC converter is used as a LED driver that is configured as a constant current source.

Figure 11: Illumination



Test possibility

Phoenix LED test

For troubleshooting see Display faults in Baseband Troubleshooting Instructions.

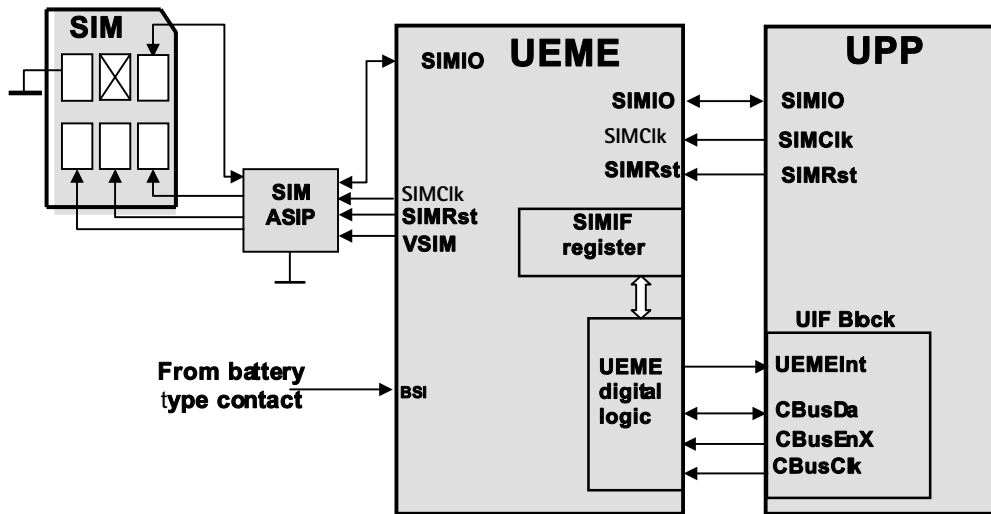
■ **SIM**

The whole SIM interface locates in UPP and UEMEK.

The interface part in the UEMEK contains power up/down, port gating, card detect, data receiving, ATR-counter, registers and level shifting buffers logic. The SIM interface is the electrical interface between the Subscriber Identity Module Card (SIM Card) and mobile phone (via UEMEK device).

Both 3V and 1.8V SIM cards are supported. A register in the UEMEK selects SIM supply voltage. It is only allowed to change the SIM supply voltage when the SIM IF is powered down.

Figure 12:UPP/UEMEK SIM Interface Connections



Test possibility

Phoenix SIM Test

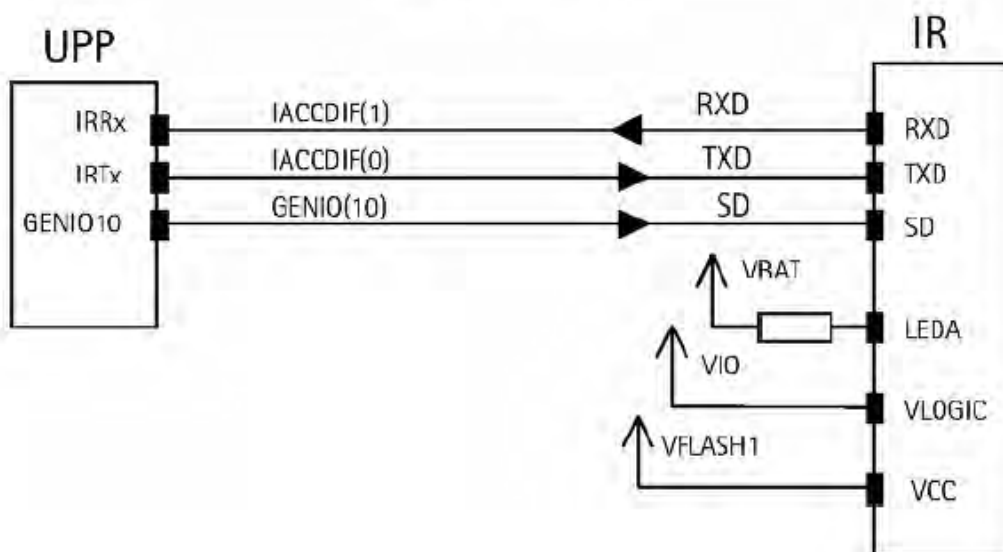
For troubleshooting, see SIM Card faults in Baseband Troubleshooting Instructions.

■ IR Module

RM-30 has an IR module. The IR link supports speeds from 9600 bit/s to 1.152 Mbit/s up to a distance of 80 cm. Transmission over the IR if is half-duplex.

The IR transceiver can be set into SIR or MIR modes. In SIR mode the transceiver is capable of transmission speed up to 115.2 kbit/s. In MIR mode faster transmission speeds are used. The maximum speed is 1.152 Mbit/s. The IR transceiver can be set into shutdown mode by setting SD pin to logic '1' for current saving reasons.

Figure 13: IR interface



Interfaces

■ BB-RF interface

The interface between the Baseband and RF can be divided into three categories:

- The digital interface from UPP to the RF ASIC (Helgo). The serial digital interface is used to control the operation of different blocks in the RF ASICs
- The analogue interface between Baseband and RF. The analogue interface consists of Tx and Rx converter signals. The power amplifier control signals TXC and AFC also come from the UEMEK.
- Reference clock interface between Helgo and UPP which supplies the 26 MHz system clock for UPP.

■ System connector interface

System connector

The system connector is a galvanic interface between phone and accessory.

Four new functions are introduced with the PopPort™ IF; Accessory Control Interface (ACI), Power Out; Stereo audio output and Universal Serial Bus (USB). The USB functionality is not supported by RM-30. The RM-30 product supports “double mono” on the earpiece lines. The MBUS function, (included in previous accessory interfaces) is not supported by this interface.

The connector is not backward compatible with DCT1, DCT2 and DCT3 accessory interfaces.

Figure 14:PopPort™ bottom connector (charger plug socket & PopPort™ system connector)

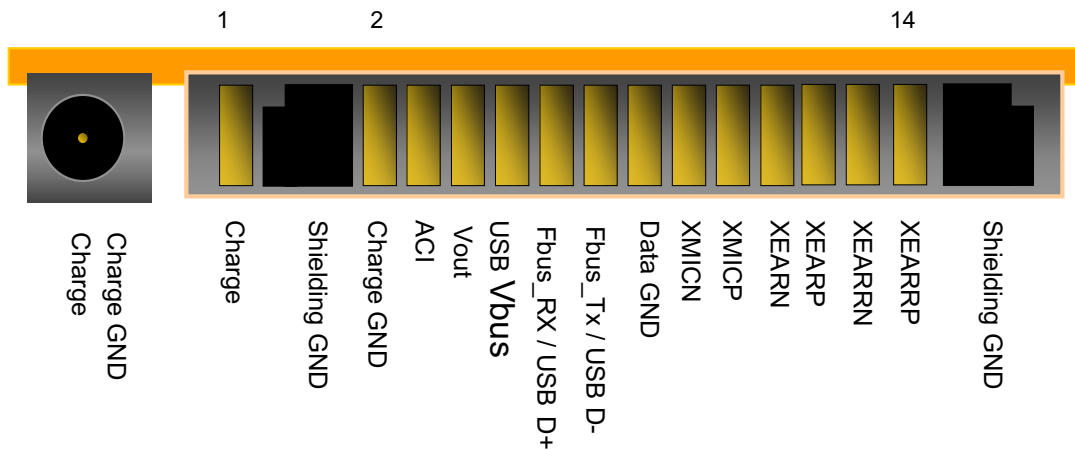


Table 11: System connector interface description

Pin #	Signal	Notes
1	VCHAR	
2	GND	Charge ground
3	ACI	Insertion & removal detection / Serial data bi-directional 1 kbit/s
4	Vout	Power supply for external accessories
5		Not used in RM-30
6	FBUS_RX	Serial data from accessory to phone / 115 kbit/s
7	FBUS_TX	Serial data from phone to accessory / 115 kbit/s
8	GND	Data ground
9	XMIC N	Negative audio in signal
10	XMIC P	Positive audio in signal
11	HSEAR N	Negative audio out signal.
12	HSEAR P	Positive audio out signal.
13	HSEAR RN	Negative audio out signal.
14	HSEAR RP	Positive audio out signal.

ACI

ACI (Accessory Control Interface) is a point-to-point, Master-Slave, bi-directional serial bus. ACI has two main features:

- The identification of accessory type is provided
- The insertion and removal detection of an accessory device
- Acting as a data bus, intended mainly for control purposes.

FBUS

FBUS is an asynchronous data bus having separate TX and RX signals. Default bit rate of the bus is 115.2 Kbit/s. FBUS is mainly used for controlling the phone in the interface to PC via DKU-5.

VOUT

The VOUT pin delivers the power supply for PopPort™ accessories, which are using the ACI or FBUS. The voltage level is 2.78V / 70mA.

DC plug

NMP standard 2- or 3-wire chargers are compatible with the charger IF. The IF does not support 3-wire charging control. Nevertheless, it is potential possible to use a 3-wire charger without PWM charging support. RM-30 uses a 3mm DC plug besides the PopPort™ IF.

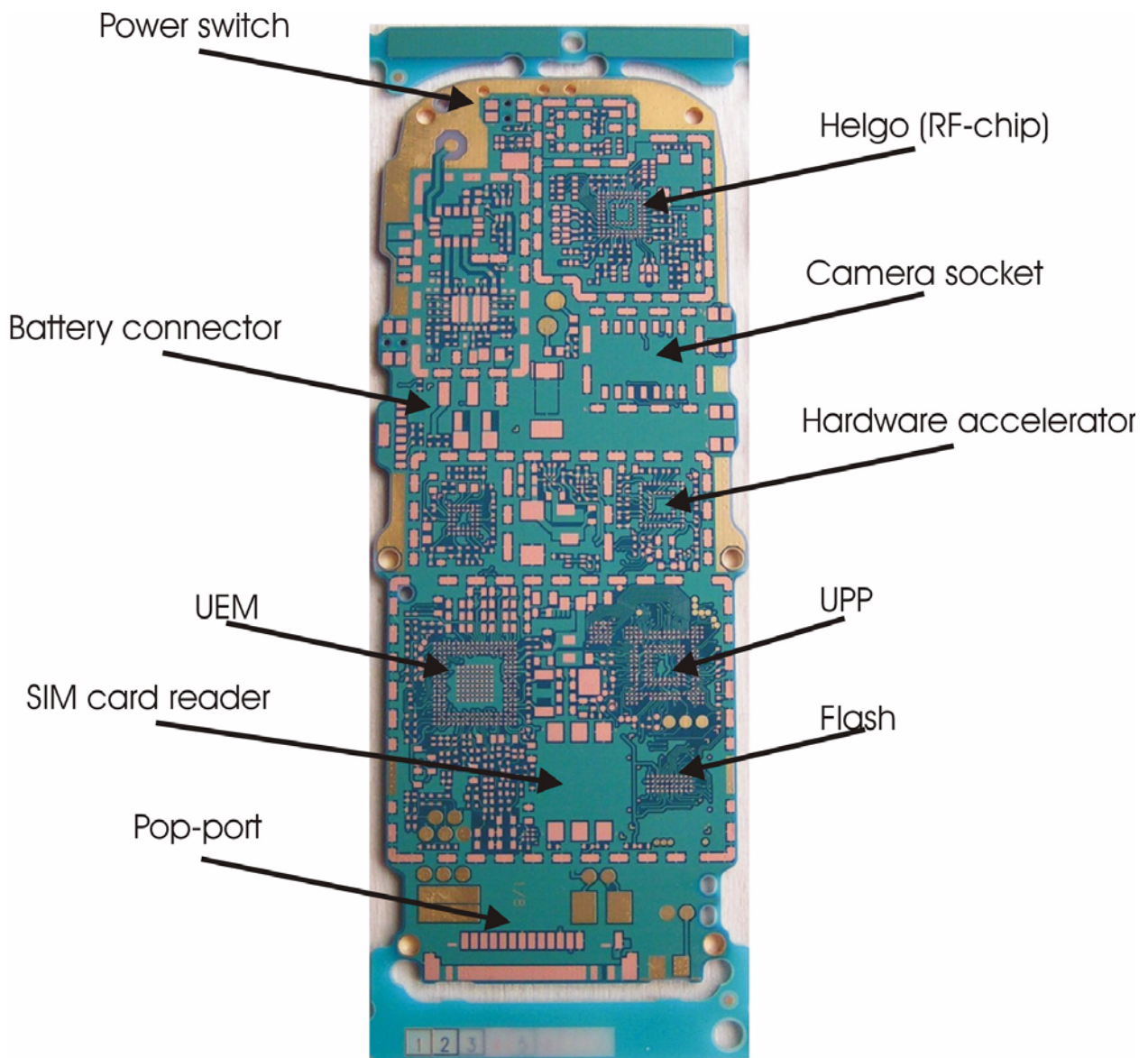
Component Replacement Hints

When exchanging components, all components must be placed properly. There is an extra challenge when:

- Components are manually replaced
- Lead free process is applicable (which is the case for all RM-30 devices)

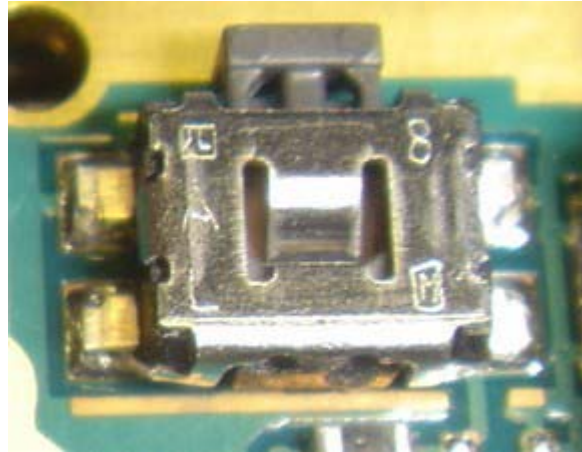
Therefore, the following replacement support and check possibilities have been implemented:

Figure 15: PWB overview



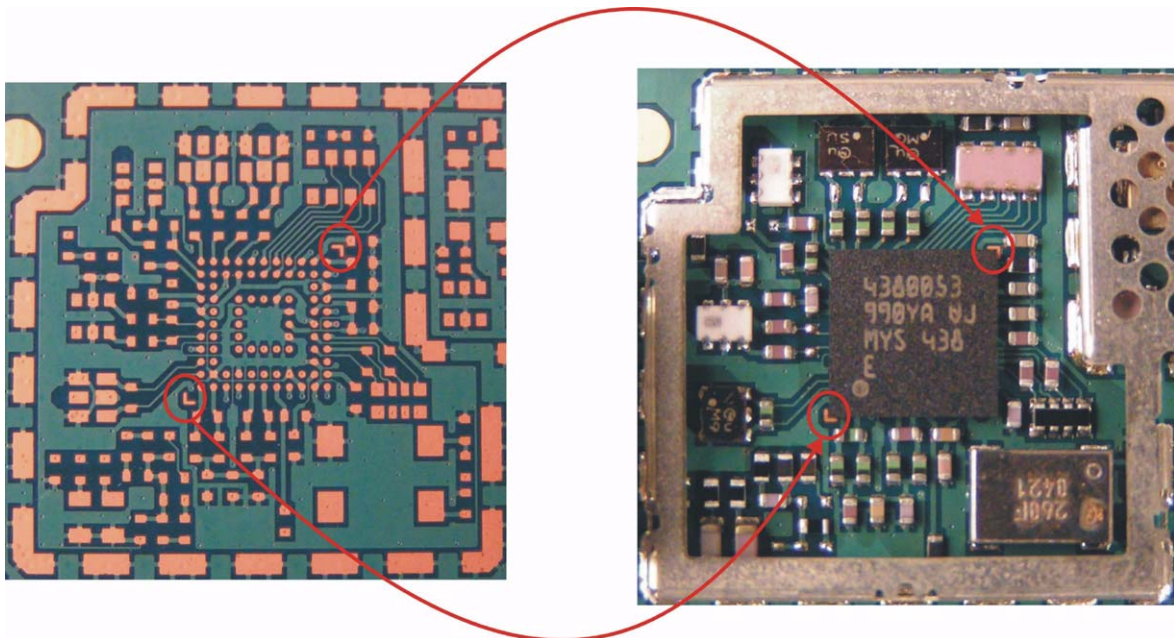
■ Power switch (S2419)

The power switch replacement has a direct influence to the phone usability and failure rates. Improper placement can cause difficulties to switch the phone on / off or increase the switch's sensitivity when dropping the phone (peeling of the switch or its pads). For proper placement, the line behind the switch needs to fit properly (as shown in the picture below, it must be centric and just visible) even after soldering to get proper functionality of the switch.



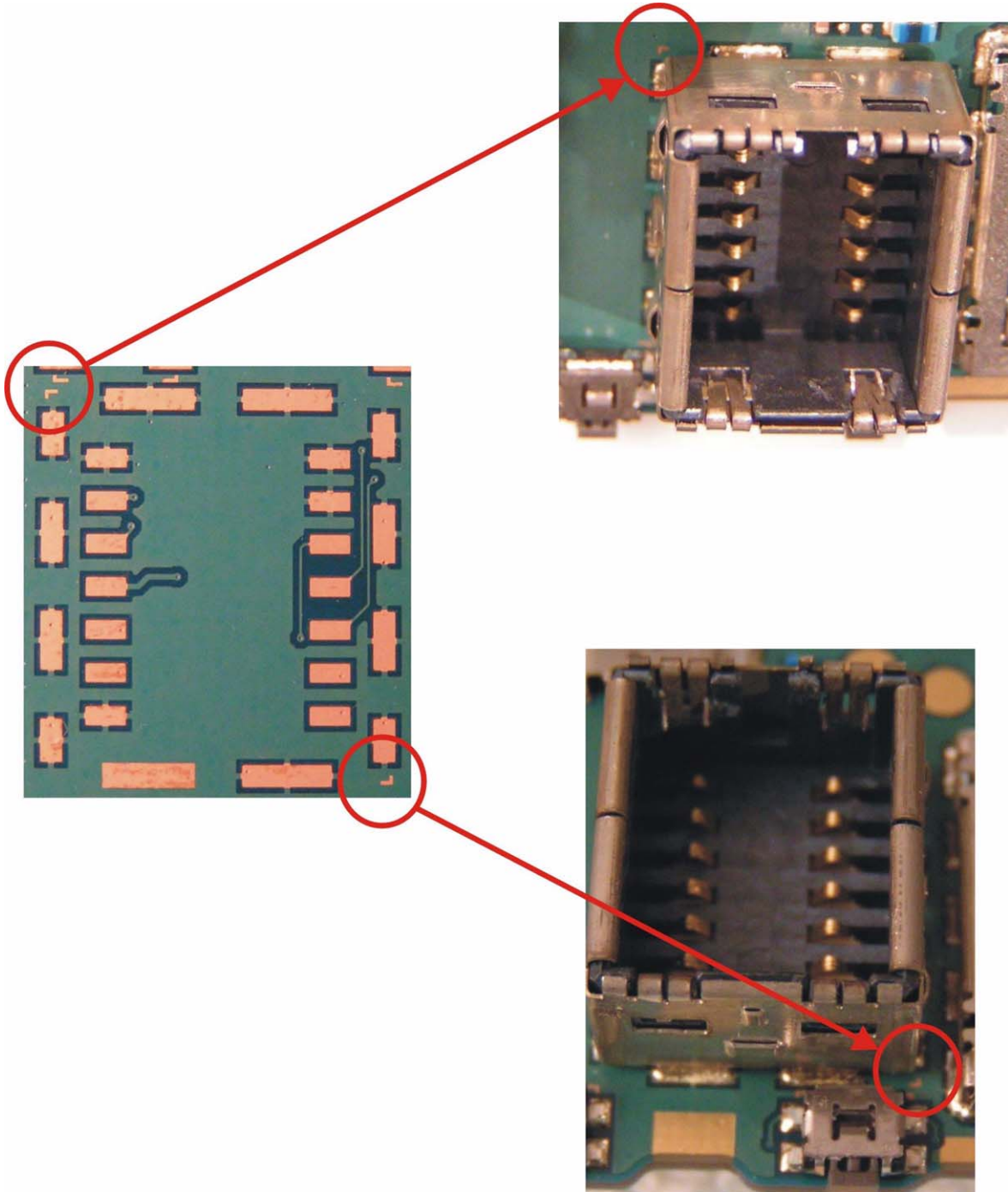
■ Helgo RF-chip (N7500)

There are also corner marks introduced in order to help checking the placement after rework. The placement shall be done with proper equipment. The corner marks indicate proper placement after the soldering process. If the component is not placed properly the re-work process must be repeated until the component fits properly.



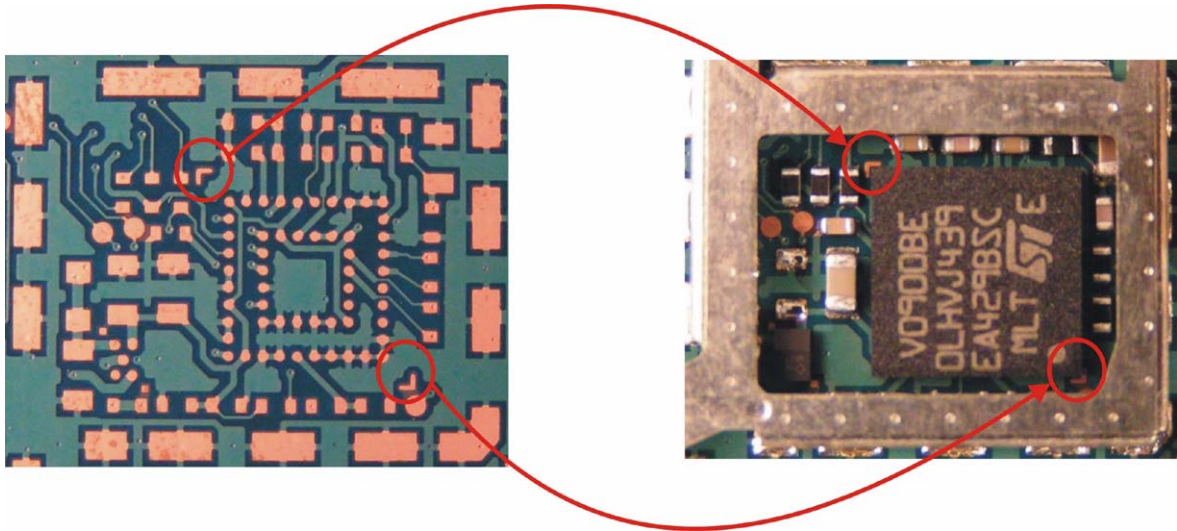
■ **Camera socket (X1470)**

There are also corner marks introduced in order to support placement and checking placement after rework process.



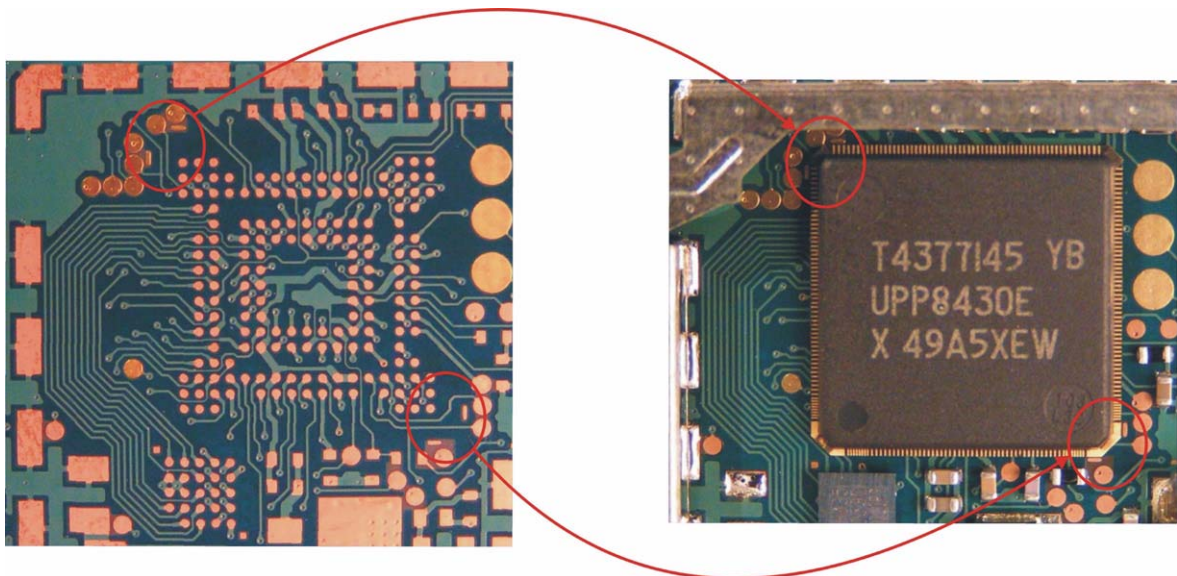
■ **Hardware accelerator (D1470)**

There are also corner marks introduced in order to enable checking placement after rework process.



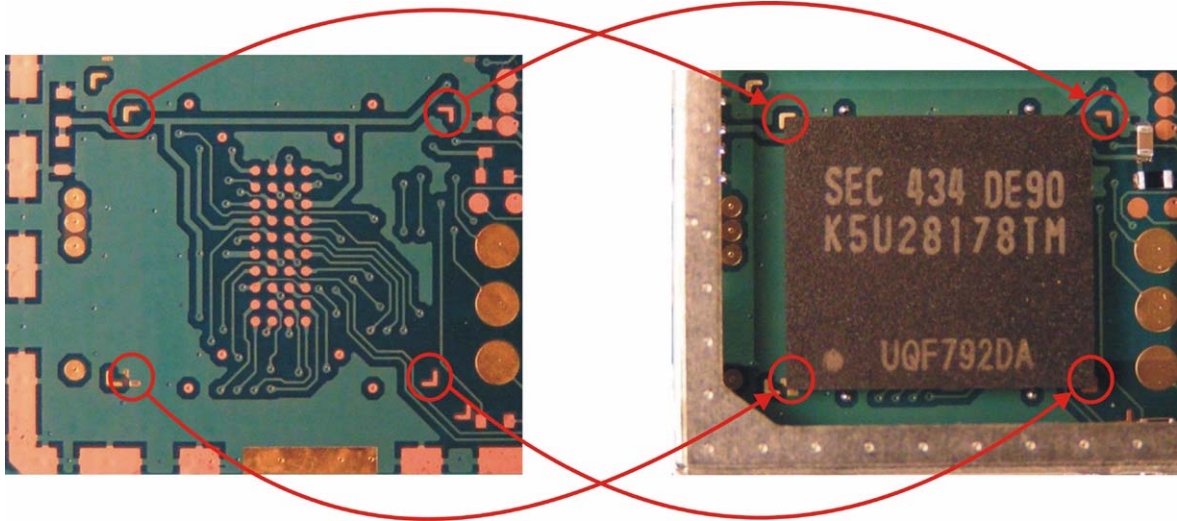
■ **UPP (D2800)**

There are also corner marks introduced in order to help checking placement after rework process.



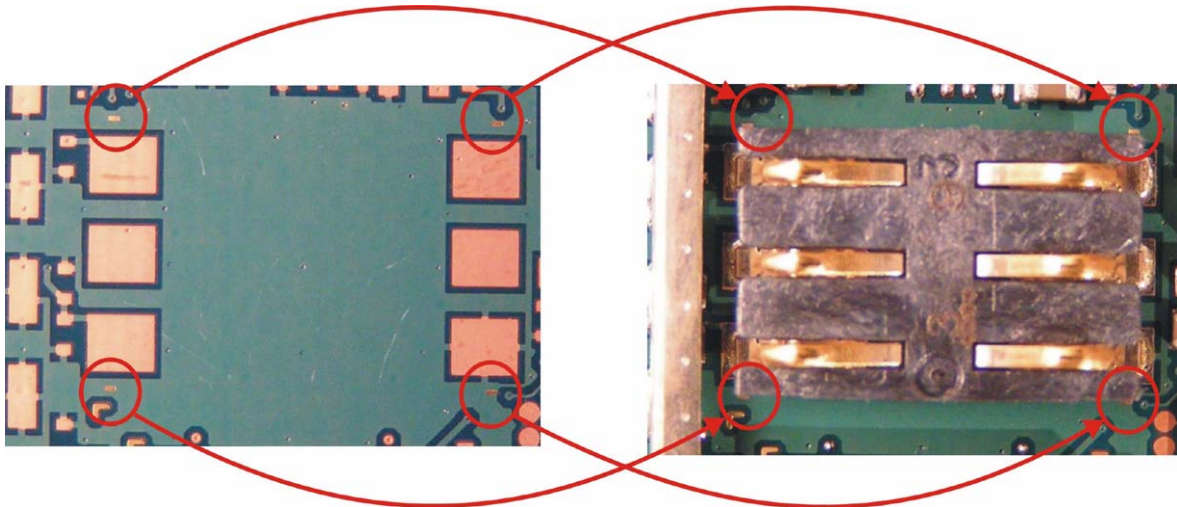
■ **Flash (D3000)**

There are some corner marks introduced.



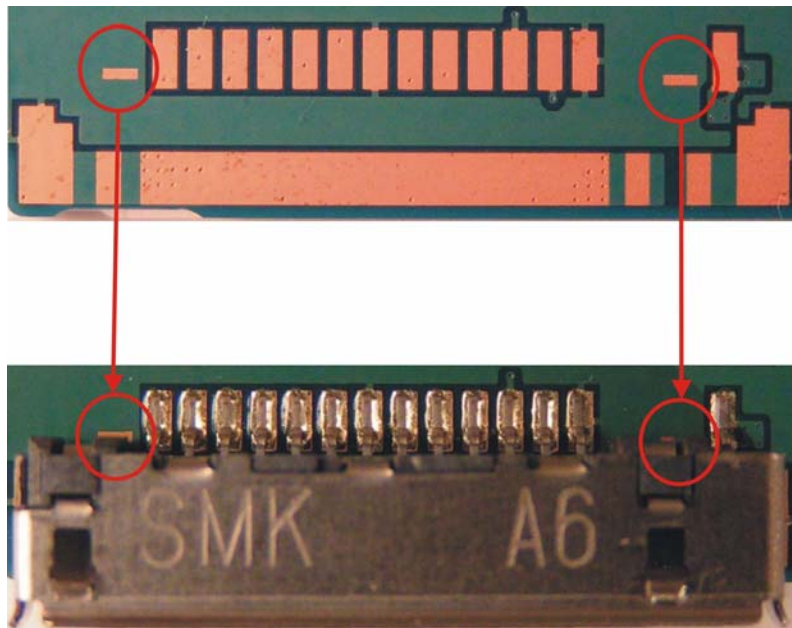
■ **SIM card reader (X2700)**

There are some corner marks introduced.



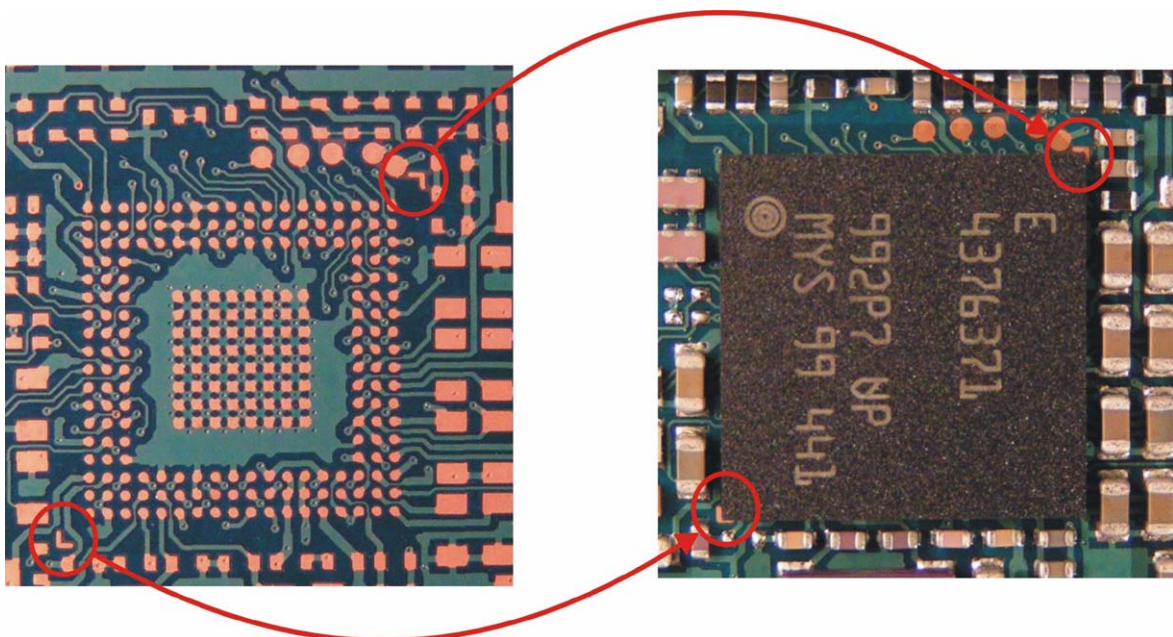
■ **System connector (X2002)**

There are also some marks introduced (bars) in order to help placing the system connector and checking placement after rework. The placement bars need to be visible (they can be partly hidden by the connector), but the connector must equally hide them in order to be parallel to the PWB. In addition, the connectors must meet their pads properly as well.



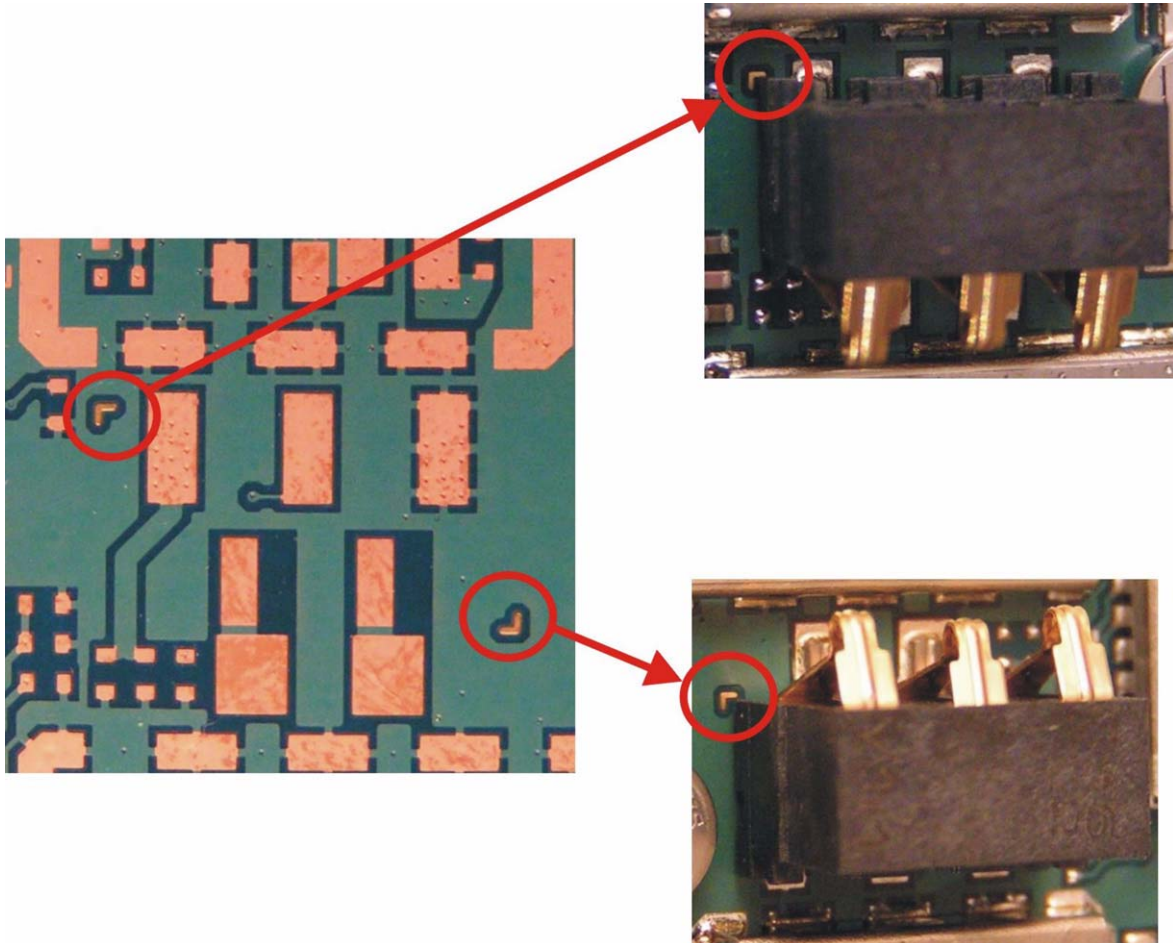
■ **UEM (D2200)**

There are also corner marks introduced in order to help checking placement after rework.



■ **Battery connector (X2000)**

There are also some corner marks introduced in order to support placement of the connector and checking placement after rework.

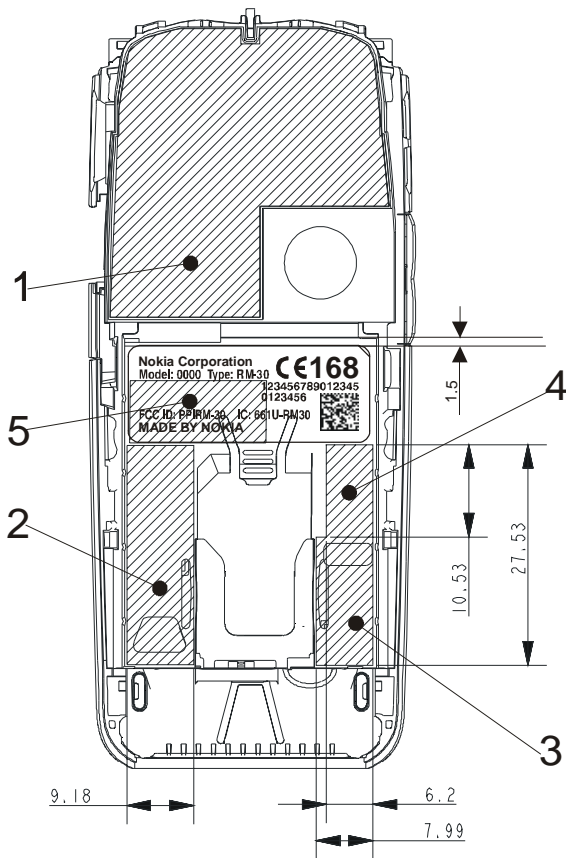








Label placement

Different countries require different labels. This guide explains where it is possible to place these labels.

In the figure below, there are numbered shaded areas (1 - 5) where labels can be placed. On the right hand side there are numbers and labels. The numbers refer to the place where the label is allowed to be placed.

The Taiwan-specific label is metalized and it is very critical to place it properly, so that the phone performance is not affected. For this reason it is allowed to place it on the named areas 2, 3 and 4, but not within the areas 1 and 5. The Chinese label, which is not metalized, has designated area 1.



- 1  China 12 x 30 not metal
- 1,2,3,4  Singapore 6x12 not metal
- 5  Malaysia 10 x 15 metal (on top of Nokia label)
- 2,3,4  Taiwan 6 x 13 metal
- 1,2,3,4  AT&T 6,2 x 25 not metal
-  Type Label 32,5 x 13 metal

RF Module Description

The RF module performs the necessary high frequency operations of the triple-band engine. Both the transmitter and receiver have been implemented by using a direct conversion architecture, which means that the modulator and demodulator operate on the channel frequency. No intermediate frequencies are used for up- or down-conversion.

The core of the RF is an application-specific integrated circuit (RF ASIC), Helgo85. The other RF key components are:

- An EDGE capable power amplifier module, which includes two amplifier chains, one for the low band (GSM900) and the other for both high bands (GSM1800 and GSM1900).
- An antenna switch module, which contains filters and switches to combine the two TX-PA outputs and three Rx chain inputs to the antenna port.
- 26 MHz reference oscillator (VCTCXO).
- 3296-3980 MHz VCO.
- Three SAW filters for Rx band filtering.
- One SAW filter for the low band (GSM900) Tx path.

The control information for the RF is coming from the baseband section of the engine through a serial bus, referred later on as RFBUS. This serial bus is used to pass the information on the frequency band, mode of operation, and synthesizer channel for the RF. In addition, exact timing information and receiver gain settings are transferred through the RFBUS.

Physically, the bus is located between the baseband ASIC called UPP and the RF ASIC. Using the information obtained from UPP, the RF ASIC controls itself to the required mode of operation and further sends control signals to the antenna switch and the power amplifier modules.

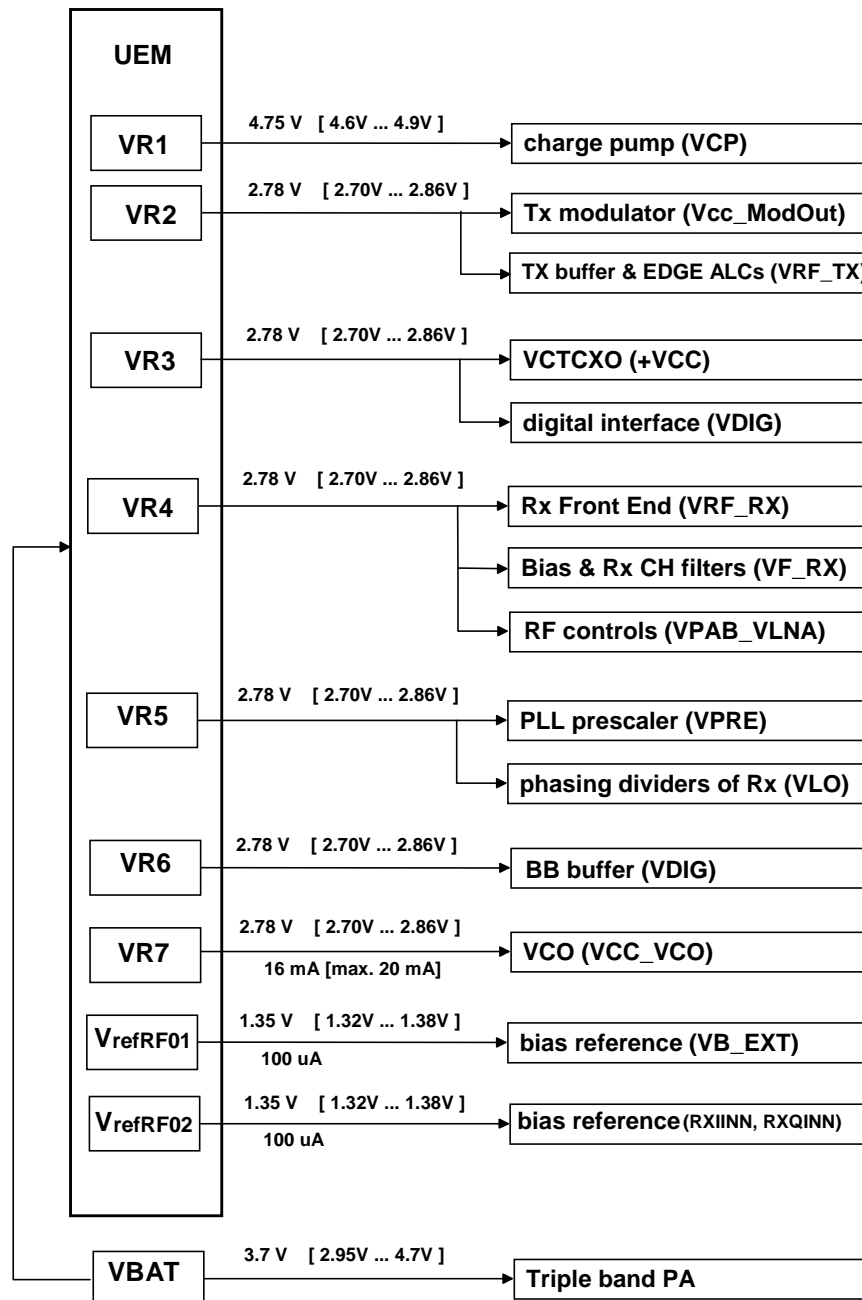
In addition to the RFBUS, there are still other interface signals for the power control loop and VCTCXO control and for the modulated waveforms (IQ signals).

The RF circuitry is located in two shielding chambers on one side of the 8 layer PWB containing the following key components: The Small Signal Chamber contains RF ASIC, reference oscillator (VCTCXO), VCO, and Rx/Tx SAW-filters (GSM900/GSM1800). The Large Signal Chamber contains the RF Power Amplifier, the Antenna Switch Module, and the Rx SAW-filter and LNA (GSM1900).

■ General specifications of the transceiver

Parameter	Unit
Cellular System	GSM900, GSM1800, GSM1900
Modulation schemes	GMSK, 8-PSK
RX Frequency Band	GSM900: 925 ... 960 MHz GSM1800: 1805 ... 1880 MHz GSM1900: 1930 ... 1990 MHz
TX Frequency Band	GSM900: 880 ... 915 MHz GSM1800: 1710 ... 1785 MHz GSM1900: 1850 ... 1910 MHz
Output Power GMSK	GSM900: +5 ... +33 dBm (3.2 mW ... 2 W) GSM1800: +0 ... +30 dBm (1.0 mW ... 1 W) GSM1900: +0 ... +30 dBm (1.0 mW ... 1 W)
Output Power 8-PSK	GSM900: +5 ... 27 dBm (3.2 mW ... 0.5 W) GSM1800: +0 ... 26 dBm (1.0 mW ... 0.4 W) GSM1900: +0 ... 26 dBm (1.0 mW ... 0.4 W)
Duplex Spacing	GSM 900: 45 MHz GSM 1800: 95 MHz GSM 1900: 80 MHz
Number of RF Channels	GSM 900: 174 GSM 1800: 374 GSM1900: 299
Channel Spacing	200 kHz (each band)
Number of TX Power Levels GMSK	GSM 900: 15 GSM 1800: 16 GSM 1900: 16
Number of TX Power Levels 8-PSK	GSM 900: 12 GSM 1800: 14 GSM 1900: 14
Sensitivity, static channel (+25°C)	GSM 900: -102 dBm GSM 1800: -102 dBm GSM 1900: -102 dBm
Frequency Error, static channel	< 0,1 ppm
RMS Phase Error	< 5.0°
Peak Phase Error	< 20.0°

Figure 17:RF power distribution diagram

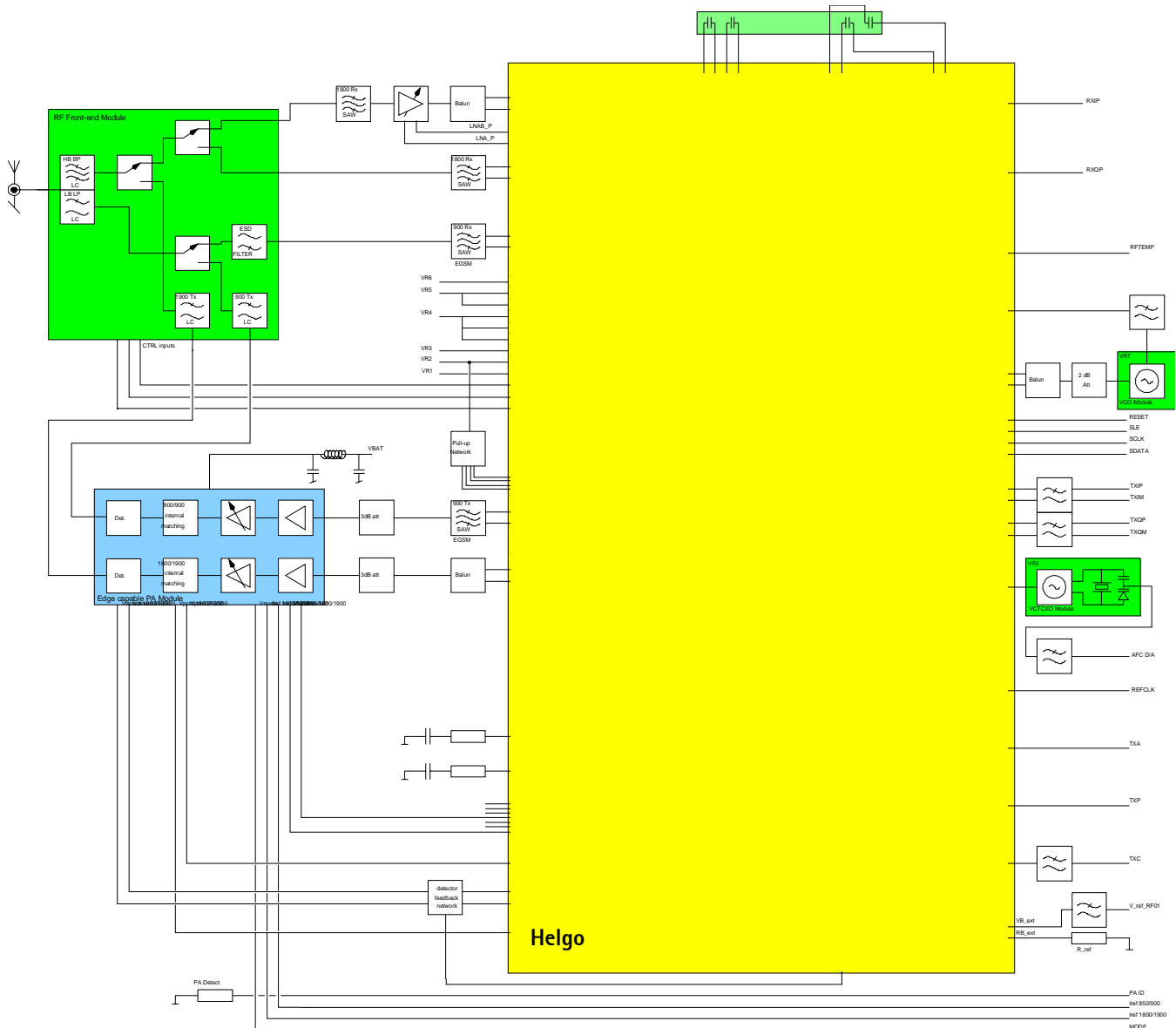


RF block diagram

RF block diagram consists of:

- Antenna switch module
- Power amplifier module
- RF ASIC
- VCTCXO module
- VCO module

Figure 18: RF block diagram



A detailed functional description is given in the following sections.

■ **Antenna switch (TX/RX switch)**

The antenna switch operates as a diplexer for the RX and TX signals. The antenna switch is controlled by the RF ASIC using the control signals VANT1, VANT2 and VANT3.

The table below shows the possible different switching states.

VANT_2	VANT_3	VANT_1	Rx1	Rx2	Rx3	Tx1	Tx2
VC1	VC2	VC3	GSM	GSM	GSM	GSM	GSM
[Volt]	[Volt]	[Volt]	900 Rx	1800 Rx	1900 Rx	900 Tx	1800/1900 Tx
0	0	0	X				
0	0	0		X			
0	2.6	2.6				X	
0	2.6	0			X		
2.6	2.6	0					X

To switch the TX-GSM 1800/1900 path both signals VANT2 and VANT3 have to be activated.

Receiver

Each receiver path is a direct conversion linear receiver. From the antenna, the received RF signal is fed to the antenna switch module where a diplexer first divides the signal to two separate paths for the low band and the two high bands. Then the paths are passing the Rx/Tx switches and the high band signal passes an additional GSM1800/1900 switch. As output of the module three separate Rx connections are available.

These signals are fed to the SAW band filters, which let only the frequencies of the wanted band pass on to the low noise amplifiers. The GSM1900 LNA is an external component, the other two LNAs are integrated in the RF ASIC.

The received signal is down converted in the demodulator mixers and amplified in the AGC gain stage to an appropriate baseband level and passed on as I and Q signal to the A/D converter in UEM for further digital signal processing.

Transmitter

The transmitter consists of two final frequency IQ-modulators and a power amplifier module with separate paths for the lower band and the upper bands, and a power control loop. The IQ-modulators are integrated in the RF ASIC, as well as the operational amplifiers of the power control loop.

The power amplifier module contains power detectors. In GMSK mode, the power is controlled by adjusting the DC bias levels of the power amplifiers. In EDGE mode, the power is controlled by adjusting ALC in Helgo RFIC.

Frequency synthesizer

One PLL synthesizer generates all the required frequencies of the three bands for Rx and Tx operation. The VCO frequency is divided by 2 or by 4 in the RF ASIC depending on the active band. This allows the generation of all the frequencies in the GSM900, GSM1800 and GSM1900 bands, both RX and TX range. The frequency synthesizer is integrated in the RF ASIC (Helgo) except for the VCTCXO, VCO, and the loop filter.

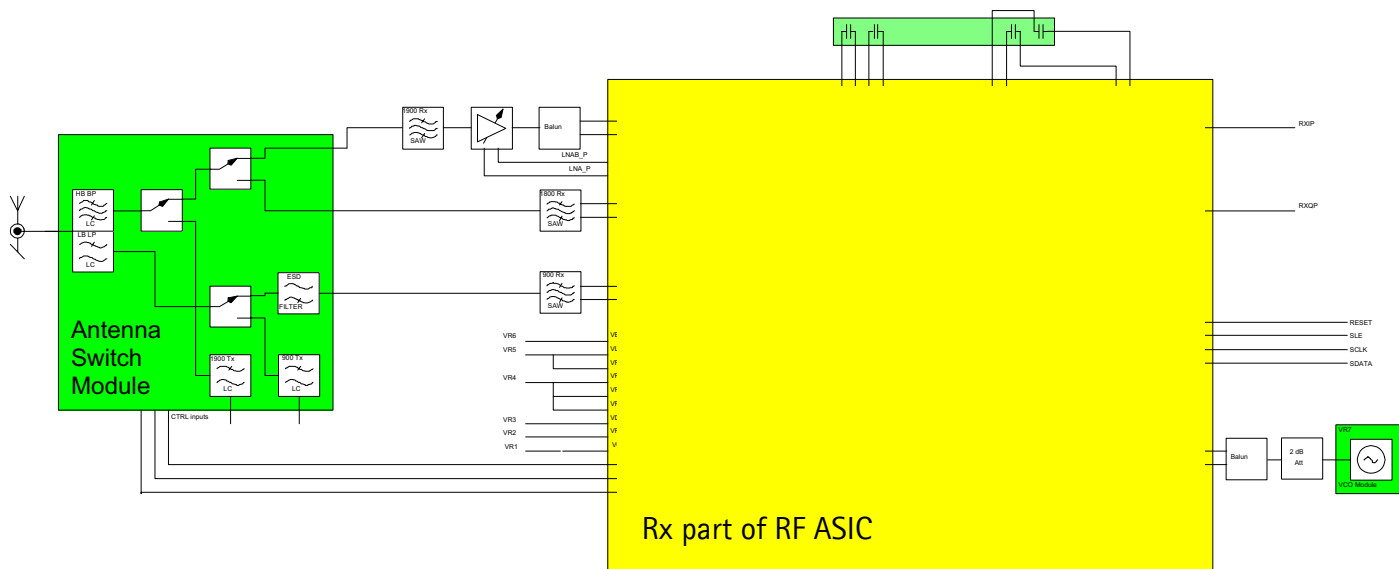
The VCTCXO (Voltage Controlled Temperature Compensated Crystal Oscillator) generates the clock frequency of 26 MHz. This frequency is buffered in the RF ASIC and fed to the UPP. Additionally, it is used as the reference frequency for the RF PLL. The frequency of the VCTCXO is locked into the frequency of the base station with the help of an AFC voltage which is generated in the UEM by an 11 bit D/A converter.

The PLL (phase locked loop) locks the VCO frequency into a stable frequency source, given by the VCTCXO. The PLL is located in the RF ASIC and is controlled through the RFBus.

The loop filter generates a DC control voltage for the VCO from the charge pump pulses of the phase detector. The loop filter determines the step response of the PLL (settling time) and contributes to the stability of the loop.

Signal paths

Receiver signal paths



From the antenna-pad, the RF signal is fed directly to the antenna switch module. Depending on the control signals VC1, VC2, VC3, the antenna port is connected to one of the Rx ports RX1, RX2, RX3. From these ports the signal is passed on to the band filters:

- GSM 900: RX1±GSM900 SAW filter
- GSM1800: RX2± GSM1800 SAW filter
- GSM1900: RX3± GSM1900 SAW filter

The antenna switch has the following typical insertion losses in the Rx mode from its input to output ports:

- GSM 900: 1.3 dB
- GSM 1800: 1.6 dB
- GSM 1900: 1.6 dB

The SAW filters provide the wanted out-of-band blocking immunity. The SAW filters have approximately 2.5 to 3 dB insertion loss.

The GSM 900 and the GSM 1800 filters are matched to the corresponding LNA inputs of the RF ASIC with a differential matching network (LC-type).

For GSM 1900, an external LNA improves the noise figure of the receiver. The external LNA provides a gain of approximately 17 dB. For conversion of the unbalanced output port to the balanced input port of the RF ASIC a balun is applied, followed by a differential matching network (LC-type).

After amplification in the RF ASIC, the RX signals are down-converted to the baseband I and Q signals and further amplified by the AGC stages. This signal is passed on to the analog-to-digital converters in UEM.

The RX paths of the RF ASIC consist of the following sub units:

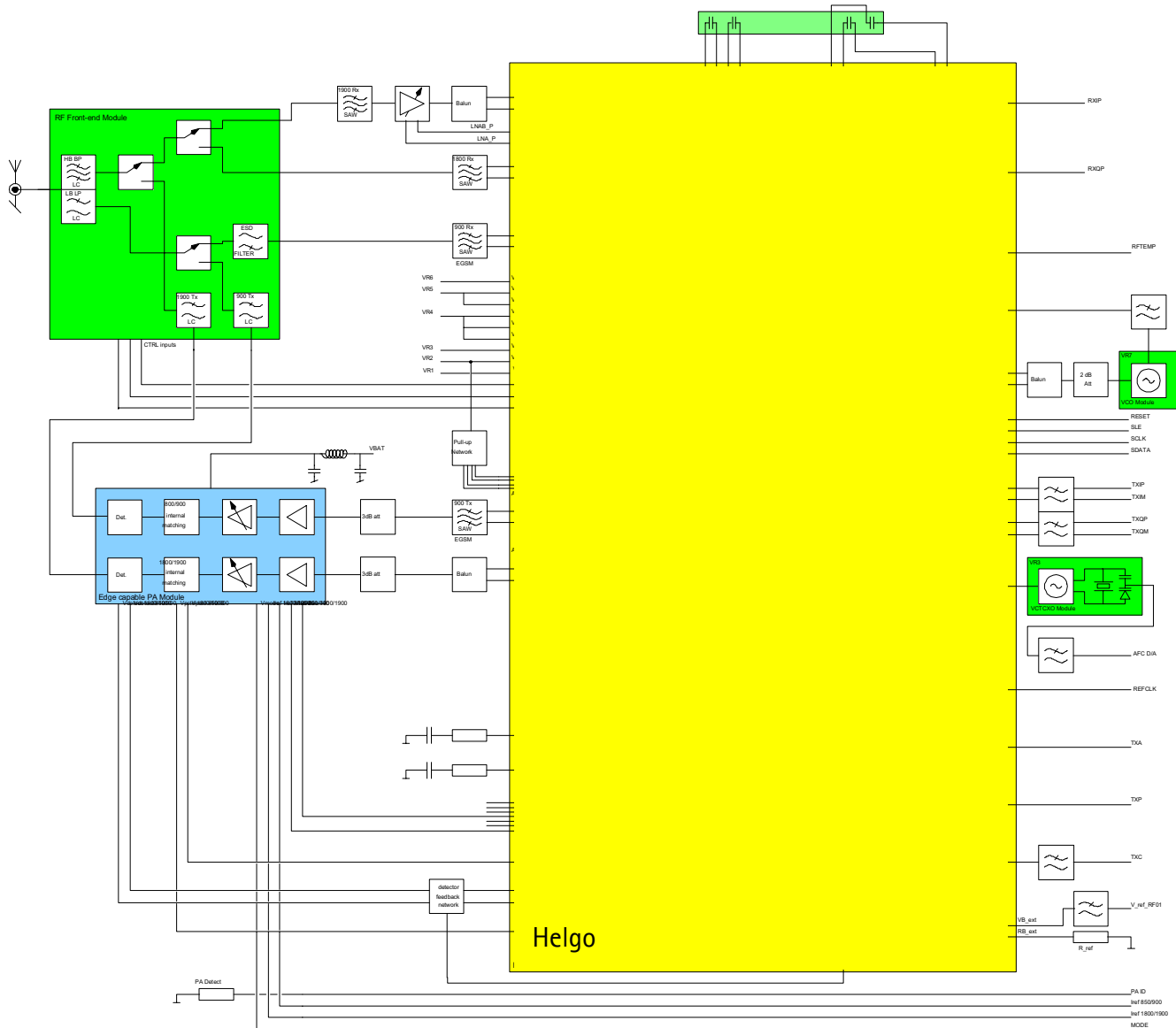
- Separate LNAs for each of the bands: GSM900, and GSM1800.
- Two PRE-GAIN amplifiers, one for GSM900 and one common for GSM1800 and GSM1900.
- Two passive I/Q mixers (MIX), one for GSM900 and one common for GSM1800 and GSM1900.

The BB signal paths consist of:

- Integrated BB channel select filter, 3rd order tunable active RC-type with equal paths for I and Q-channel. Each channel consists of 2 stages, 1st stage (DTOS) is a single ended converter with 1st order RC filter, 2nd stage is an active RC modified Sallen-Key biquad.
- Automatic gain control (AGC): DTOS has two gain stages producing a 6 dB or 18 dB gain.
- Attenuators in AGC-path.
- DC compensation / AGC amplifiers.

The differential base band amplifiers are internally DC-coupled. Their common mode levels are set equal to the external reference voltage VrefRF01. The base band outputs RXIP and RXQP are single-ended and connected directly to the differential ADC inputs (RXI->RXIINP and RXQ->RXQINP) of the UEM-ASIC. Its common mode level is set equal to the external reference voltage VrefRF02.

Transmitter signal paths



The baseband I and Q signals, coming from UEM, are mixed up to the transmitting frequency in the RF ASIC.

The low band signal passes a SAW band filter. The SAW filter converts the balanced output signal of the RF ASIC to a single-ended signal for the power amplifier input.

The high band signal passes a balun to convert it to a single-ended signal.

Both paths are connected to the power amplifier module via a 1dB attenuator. This module generates the required RF level to transmit a 2W signal in the low band and a 1W signal in the two high bands. It contains two separate amplifiers for low band and high band.

The output signals of the PA module are fed to the antenna switch module, where the active signal is connected to the antenna port.

In GMSK mode, the output signal of the RF ASIC has constant level as the ALC amplifiers are set to constant gain. The different power levels are generated by the gain variation of the power amplifier.

In EDGE mode, the ALC amplifiers generate the different power levels and the PA is set to constant gain.

Frequency synthesizer signals

The reference oscillator is implemented as Voltage Controlled Temperature Compensated Crystal Oscillator (VCTCXO) module. The component is located in the Small Signal chamber. The VCTCXO generates the clock frequency of 26 MHz.

The reference oscillator has two functions:

- Reference frequency for the PLL synthesizer.
- System clock for baseband part. The frequency is buffered in the RF ASIC and fed to the UPP (signal VCTCXO = 26 MHz, output REFOUT of the RF ASIC).

The frequency of the VCTCXO is locked into the frequency of the base station with the help of the AFC signal. This AFC voltage is generated in the UEM by an 11 bit D/A converter and tunes the oscillator.

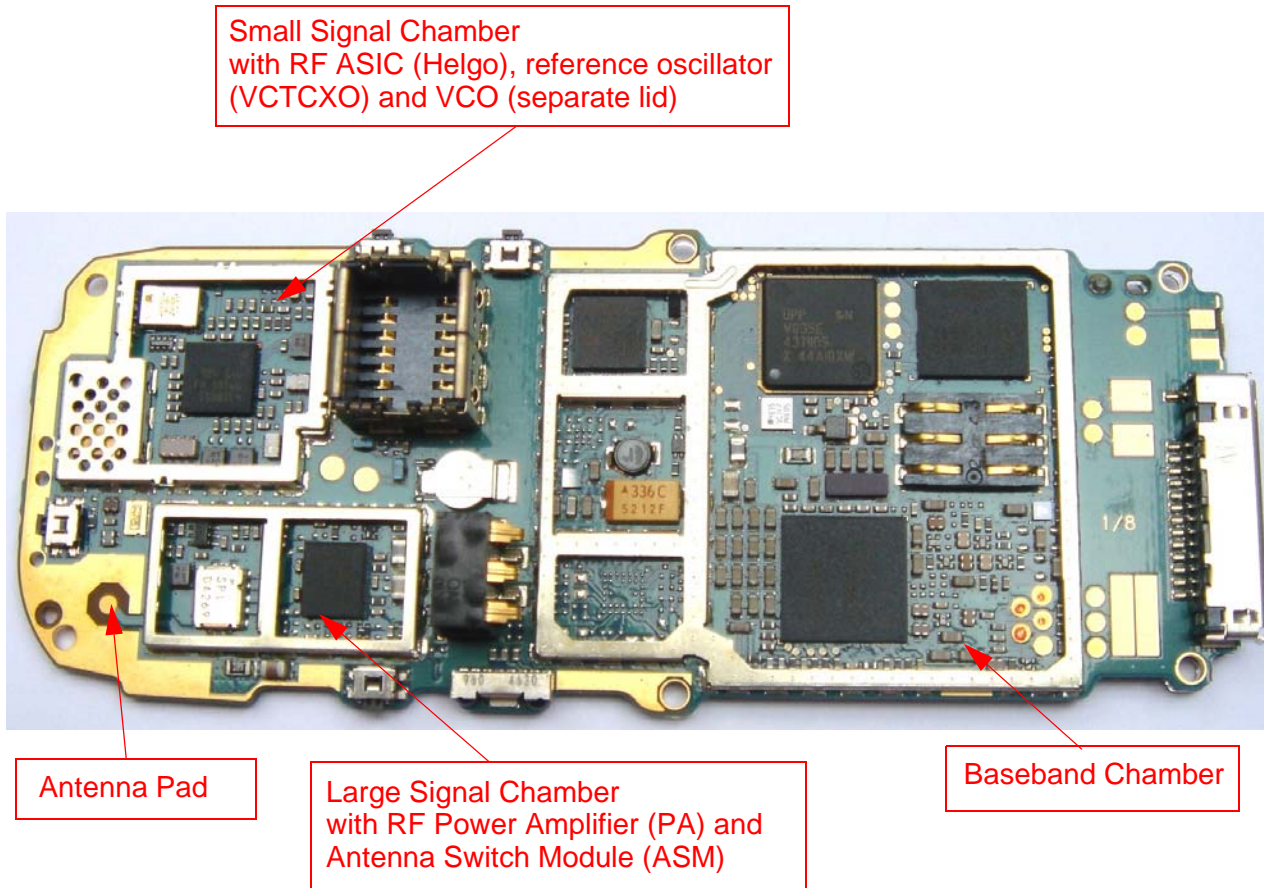
The AFC voltage is calculated using the values "AFC value" and "AFC slope", which are determined during Rx calibration of the low band.

The VCO is able to generate frequencies in the range of 3296MHz to 3980MHz. The actual frequency is controlled by a PLL (Phase locked loop) circuit, which compares the VCO frequency to the reference frequency from the VCTCXO. The charge pump of the PLL generates pulse to charge/discharge the capacitors in the loop filter. The output voltage of this filter tunes the frequency of the VCO.

The valid range of V_c is 0.7V– 3.8V when the PLL is in steady state. The typical tuning sensitivity is 250MHz/V.

Printed Wiring Board

Figure 19: Assembled PWB with shielding chambers



List of RF key components:

Position	Component Name	Supplier and Description
Z7800	Antenna Switch Module ASM	1) Hitachi Metals, M090QV
		2), 3) Murata, SPq* DA269 *q means date code which will change
Z7802	SAW1800 RX	1) FMD, B2CC
		2), 3) Murata, SAFEKG84MFC0F04
Z7801	SAW1900 RX	1) Epcos, LF55F
		2), 3) Murata, SAFEJ1G96KB0F04
N7500	RF ASIC (Helgo 8.5)	1), 2), 3) ST Microelectronics
V7800	LNA 1900 RX	1), 2), 3) Infineon
G7501	VCTCXO	1) Kyocera, KT20a
		2), 3) NDK
G7500	VCO	1) Matsushita, ENFVK3W2F07
		2), 3) FDK, WB002G
N7700	TX-PA	1) Renesas, PF09015B
		2), 3) RFMD, PA RF9250
Z7803	SAW900 RX	1) Epcos, LL73B
		2), 3) Murata, SAFEK942MFL0F04
Z7700	SAW900 TX	1) FMD, B29JP
		2), 3) Murata, SAFEK897MFM0F04

Assembly variants: Components assembled on one and the same board are marked with 1) respectively 2) or 3) for variant BOM 1 respectively for variants BOM2.

Nokia codes for components without full code numbers are marked with *, the codes will be replaced with the corresponding numbers as soon as available.

Nokia Customer Care




Appendix 7A: Differentiation between RM-30 and RM-31

Differentiation between 900 MHz and 850 MHz (US) version (RM-30 vs. RM-31)

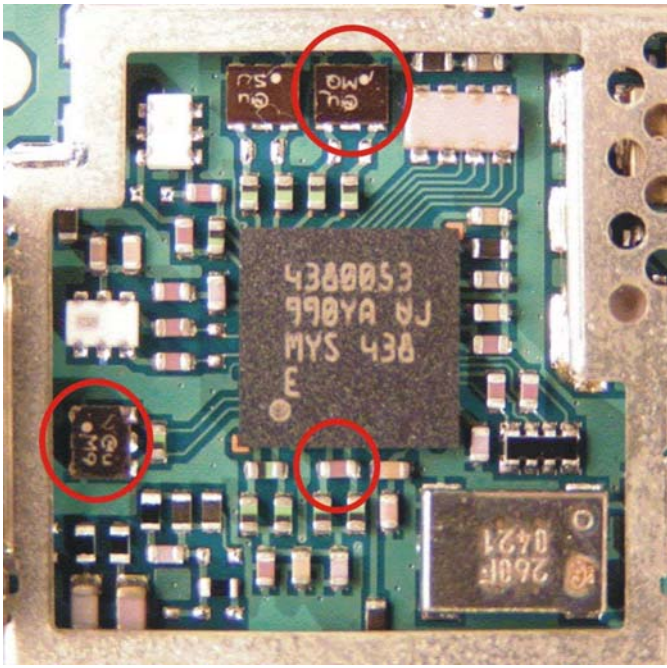
In order to serve all markets, also an US version with 850 MHz frequency support has been implemented. There are only a few, but very important differences between these versions.

■ Antenna radiator (I039) and deco foil (I041)

The antenna radiator has been adjusted for optimum performance for a particular frequency. The radiator is covered with a deco foil and can be easily distinguished:

EU 900 MHz (EU, APAC, China, LTA) RM-30	US 850 MHz (US) RM-31
	
	
<p>Please note the PFIAF-EU sign on the B-cover which indicates the 900 MHz-band.</p>	<p>Please note the PFJAF-US sign on the B-cover which indicates the 850 MHz-band</p>
	

Since there are also different hardware versions for these phones, following differences are applicable:

Picture (EU/APAC version)			
Version		900 MHz (EU, APAC, China, LTA) RM-30	850 MHz (US) RM-31
C7511		Capacitor Value: 1p2	Capacitor Value: 1p5
TX Z7700	BOM 1	SAW FILT 897.5+-17.5MHz/3dB 2.0x1.6x0.57 Supplier: Fujitsu	SAW FILT 836.5+-12.5MHz 2x1.6 Supplier: Murata
	BOM 2	SAW FILT 897.5+-17.5MHz/3dB 2.0x1.6x0.57 Supplier: Murata	
RX Z7803	BOM1	SAW FILT 942.5+-17.5MHz/ 2.1dB 2x1.6x0.68 Supplier: Epcos	SAW FILT 881.5+-12.5MHz 2x1.6 Supplier: Murata
	BOM 2	SAW FILT 942.5+-17.5MHz/3dB 2x1.6 Supplier: Murata	

Note: If one of these components needs to be exchanged, please take care that the right one is used. The phone will not work properly when a wrong component has been used. In such a case the tuning shall be redone.

MCU-SW

There is no difference in the MCU-SW. The SW supports basically all bands. The definition if the phone is a 850 or a 900 MHz phone is done in production and decides if the phone is a 850 or 900 MHz phone during boot up.

MCU flashing will not influence this setting in the flash and therefore will not have any influence on this.

PP Flags (variant specific settings) are set in production as well (label place). Those variant specific settings are set after the MCU flashing and are dependent on the chosen product variant.

Note: Please ensure that the proper product code is chosen before flashing.

■ Tuning

Since the tuning is band specific, please refer to the corresponding chapters in the Service Manual. The tuning data is also in the classified flash area and when the phone is re-flashed this data is not influenced at all.

Flash exchange

When the flash is to be exchanged, the following steps need to be done:

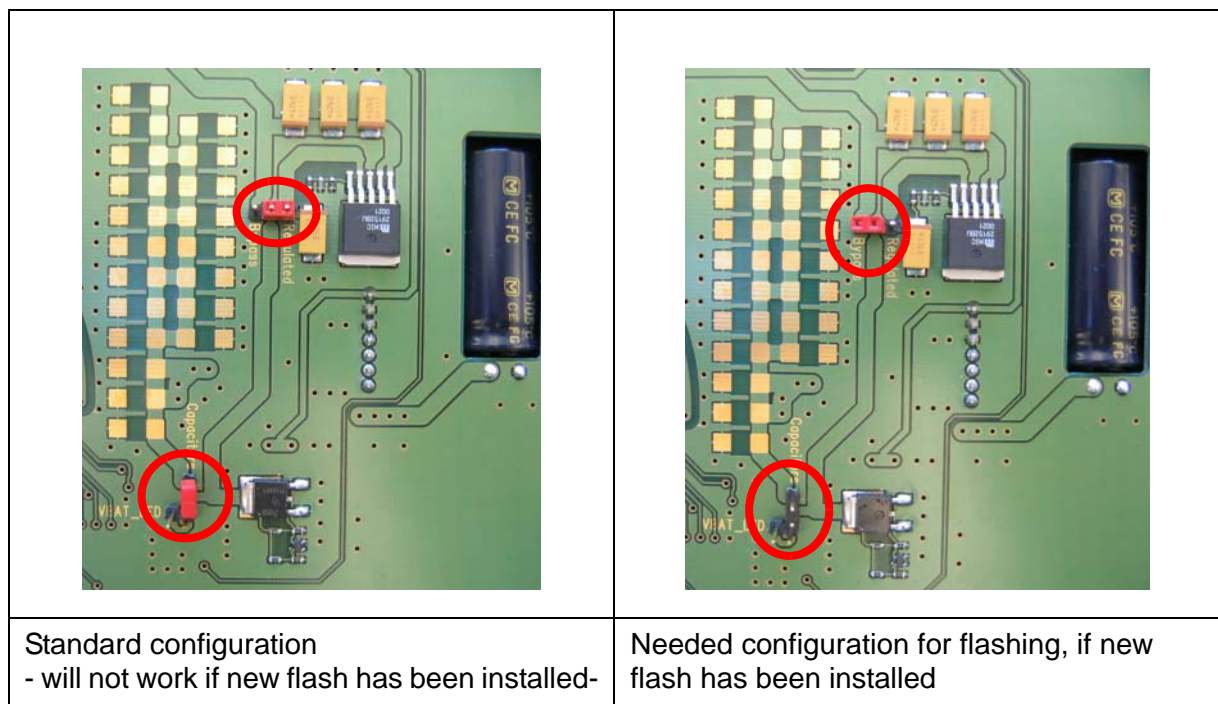
1. Flash the phone with proper MCU-SW.

For flashing with JIG:

The power supply must be connected to the Prommer Box (FPS-8)

For the first flashing procedure of a flash device, it is necessary to separate the capacitor on the backside of the JIG (by removing one jumper named capacitor). Please see the picture below. Take care that there is no jumper connecting the contacts before flashing. Otherwise, the UEM internal watchdog will hinder the flashing procedure because the power supply will not be shut down completely.

Set the other jumper to bypass.

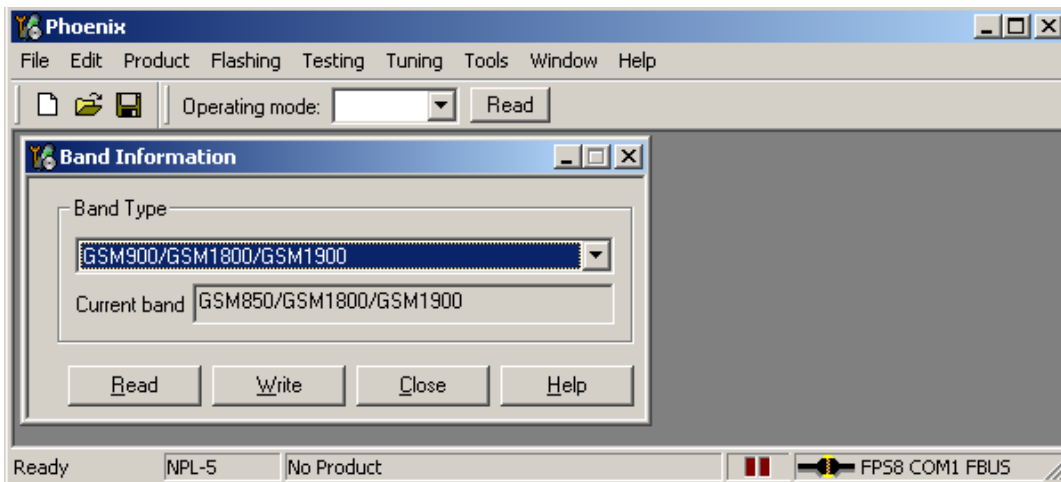


After flashing, insert the jumper “capacitors” above the cut PWB in order to connect the capacitor for power supply. This is needed for proper phone operation for the next steps.

If needed, insert the jumper for regulated voltage supply as well.

1. IMEI / SimLock rebuild (like usual).
2. Redefine the frequency version.

Use the menu 'Tuning' † 'Band Information' and choose the proper band, then press 'Write'

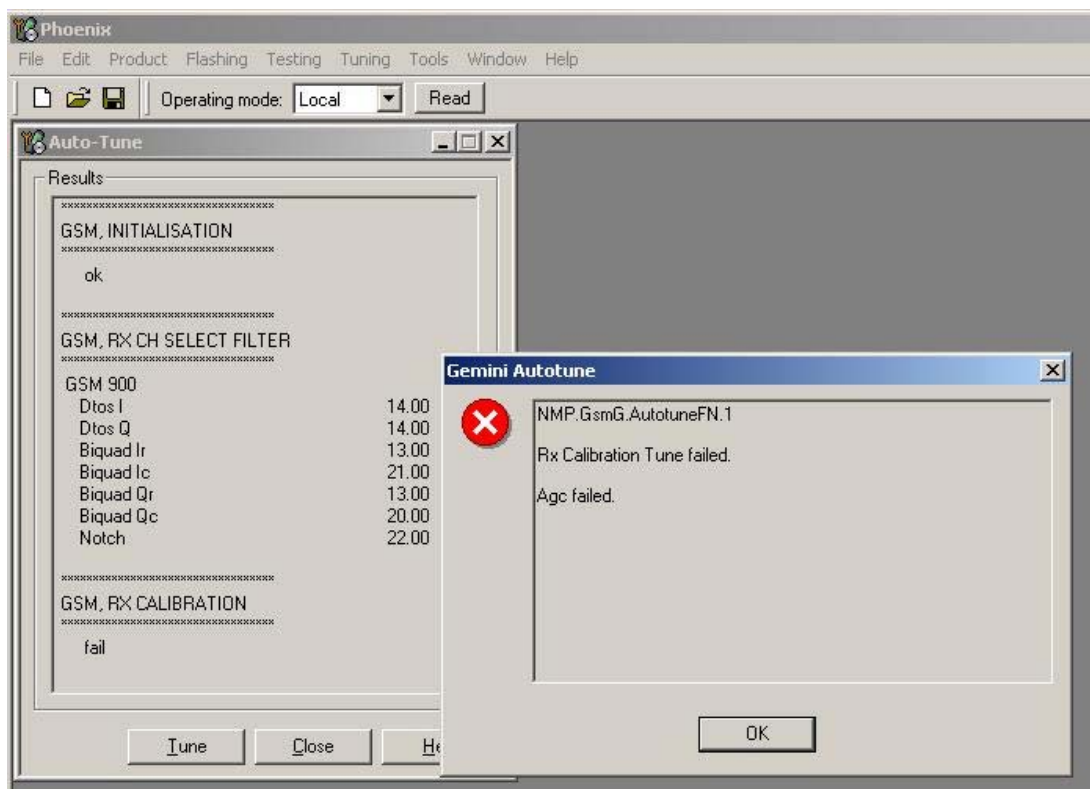


Tuning and testing

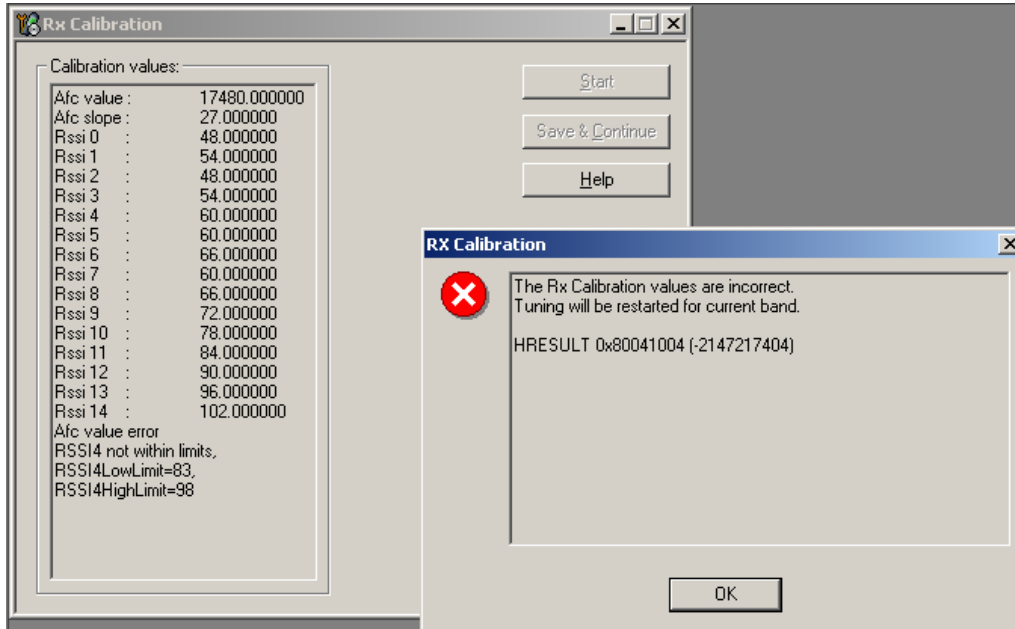
Perform the Auto-Tuning procedure as usual.

RxChannelSelectFilterCalibration will be done properly without any error message even if the wrong band information was entered.

When performing RxCalibration and during the lowest band (850 or 900 MHz) tuning procedure, an error message appears (Afc-u.Agc- values) if the wrong band information was entered.



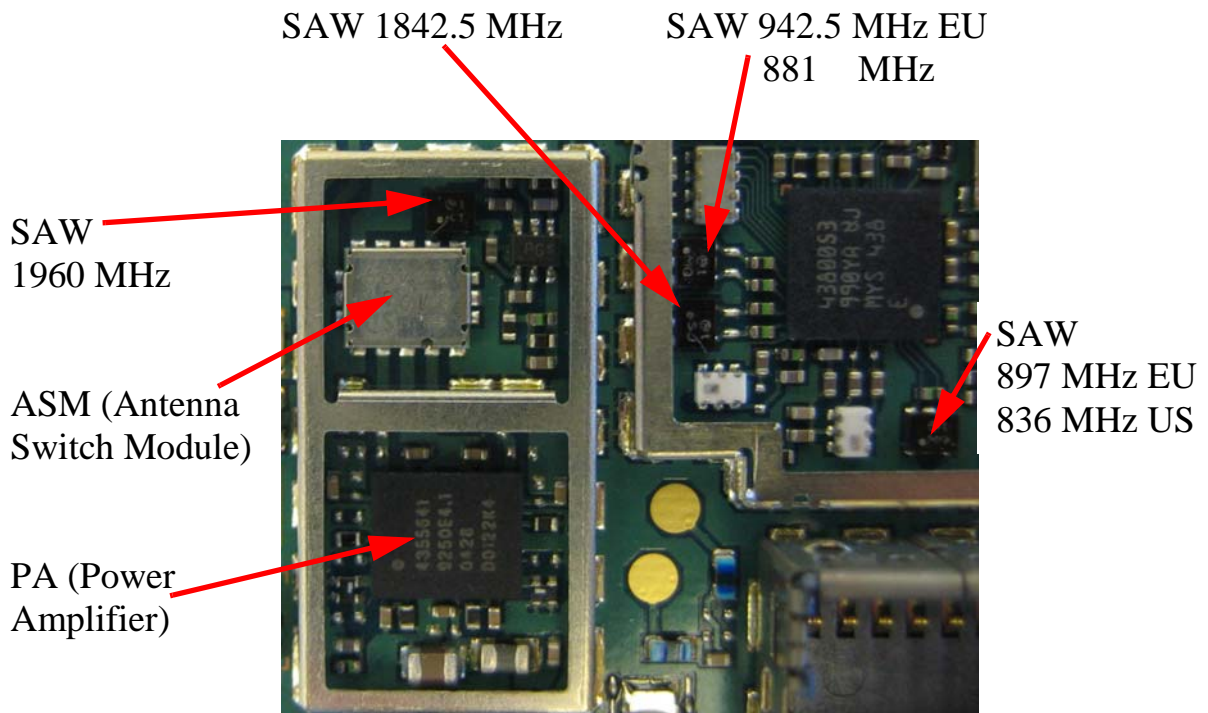
When performing manual RxCalibration and during the lowest band (850 or 900 MHz) tuning procedure, an error message appears (Afc-u.Agc- values) if the wrong band information was entered.



Power Amplifier / Antenna Switch Exchange / SAW Filter

When one of these components needs to be exchanged, a similar component (the same vendor and code) needs to be used for replacement.

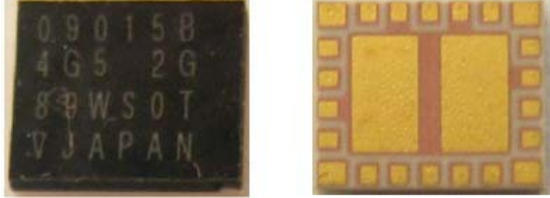
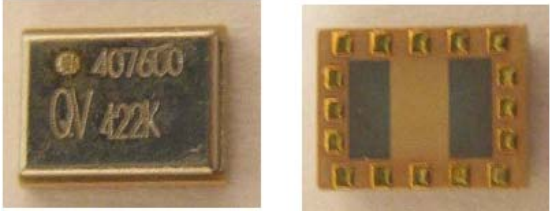
For each BOM only one set of components is used. **Parts must not be mixed-up!**



The following configurations are applicable:

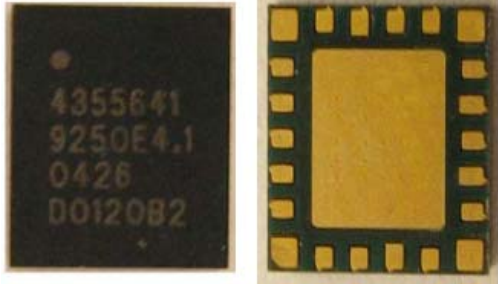
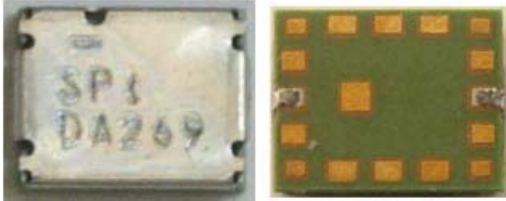
BOM 1 Start-up version in EMEA, APAC and China:

Note: BOM can easily be recognized by comparing ASM or PA.

<p>PW AMP PF09015B CUT8.9 MICRO PA GSM/EDGE</p> 	<p>RENESAS</p>
<p>DIPL+3SW824-960/1710-1990MHz5.4*4.0mm²</p> 	<p>HITACHI</p>
<p>SAW FILT 897.5+-17.5MHz/3dB 2.0x1.6x0.57</p>	<p>FUJITSU</p>
<p>SAW FILT 1842.5+-37.5MHz/2.8dB 2x1.6</p>	<p>FUJITSU</p>
<p>SAW FILT 1960+-30MHz/3dB 2x1.6x0.68</p>	<p>EPCOS</p>
<p>SAW FILT 942.5+-17.5MHz/2.1dB 2x1.6x0.68</p>	<p>EPCOS</p>

BOM 2 EMEA, APAC, China, LTA and US:

Note: BOM can easily be recognized by comparing ASM or PA.

<p>PW AMP PF09015B CUT8.9 MICRO PA GSM/EDGE</p> 	RFMD	
<p>DIPL+3SW824-960/1710-1990MHZ5.4*4</p> 	Murata	
SAW FILT 897.5+-17.5MHz/3dB 2.0x1.6x0.57	Murata	EU only
SAW FILT 1842.5+-37.5MHz/2.8dB 2x1.6	Murata	
SAW FILT 1960+-30MHz/3dB 2x1.6x0.68	Murata	
SAW FILT 942.5+-17.5MHZ/3DB 2X1.6	Murata	EU only
SAW FILT 836.5+-12.5MHZ 2X1.6	Murata	US only
SAW FILT 881.5+-12.5MHZ 2X1.6	Murata	US only